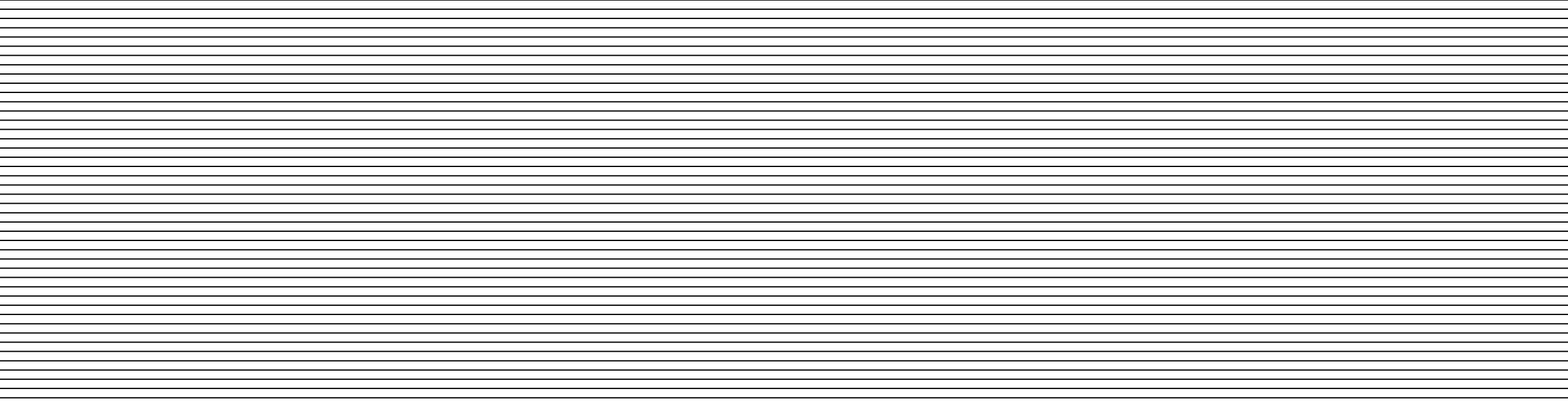
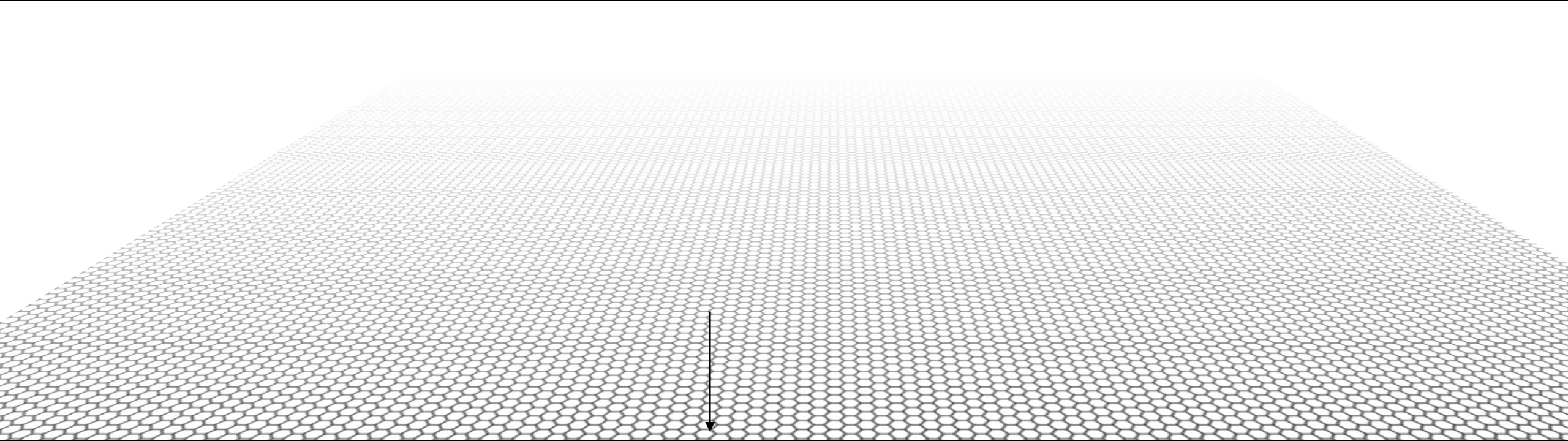
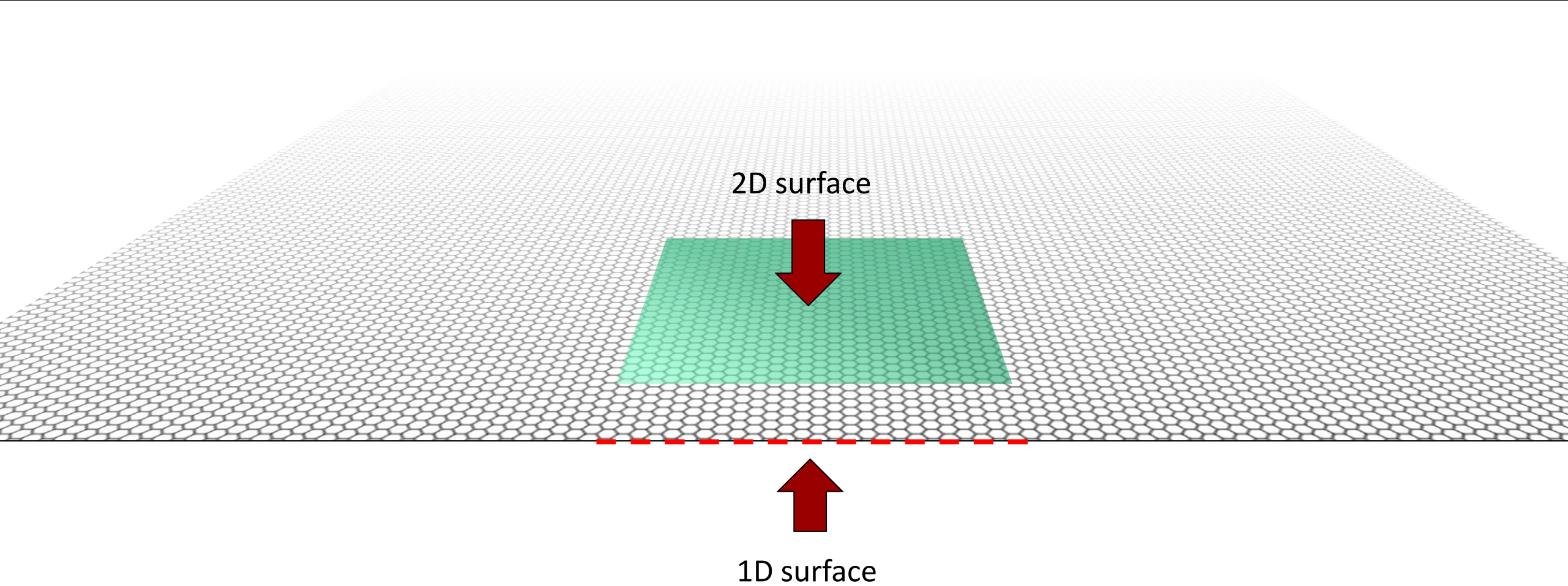


Van der Waals epitaxy

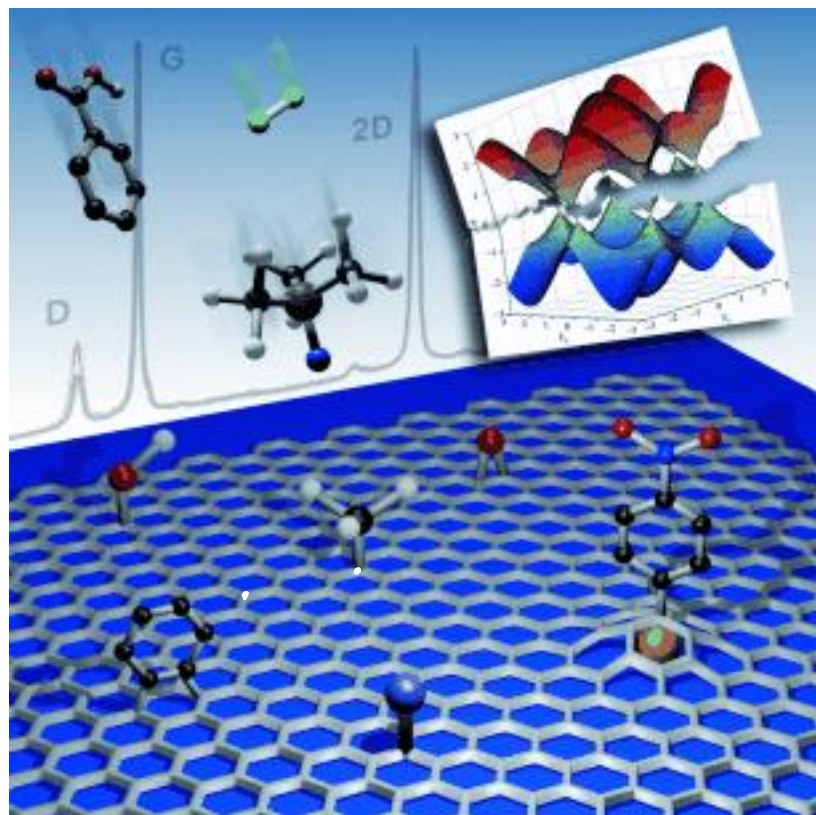
Peter Bøggild, Physics Department, Technical University of Denmark



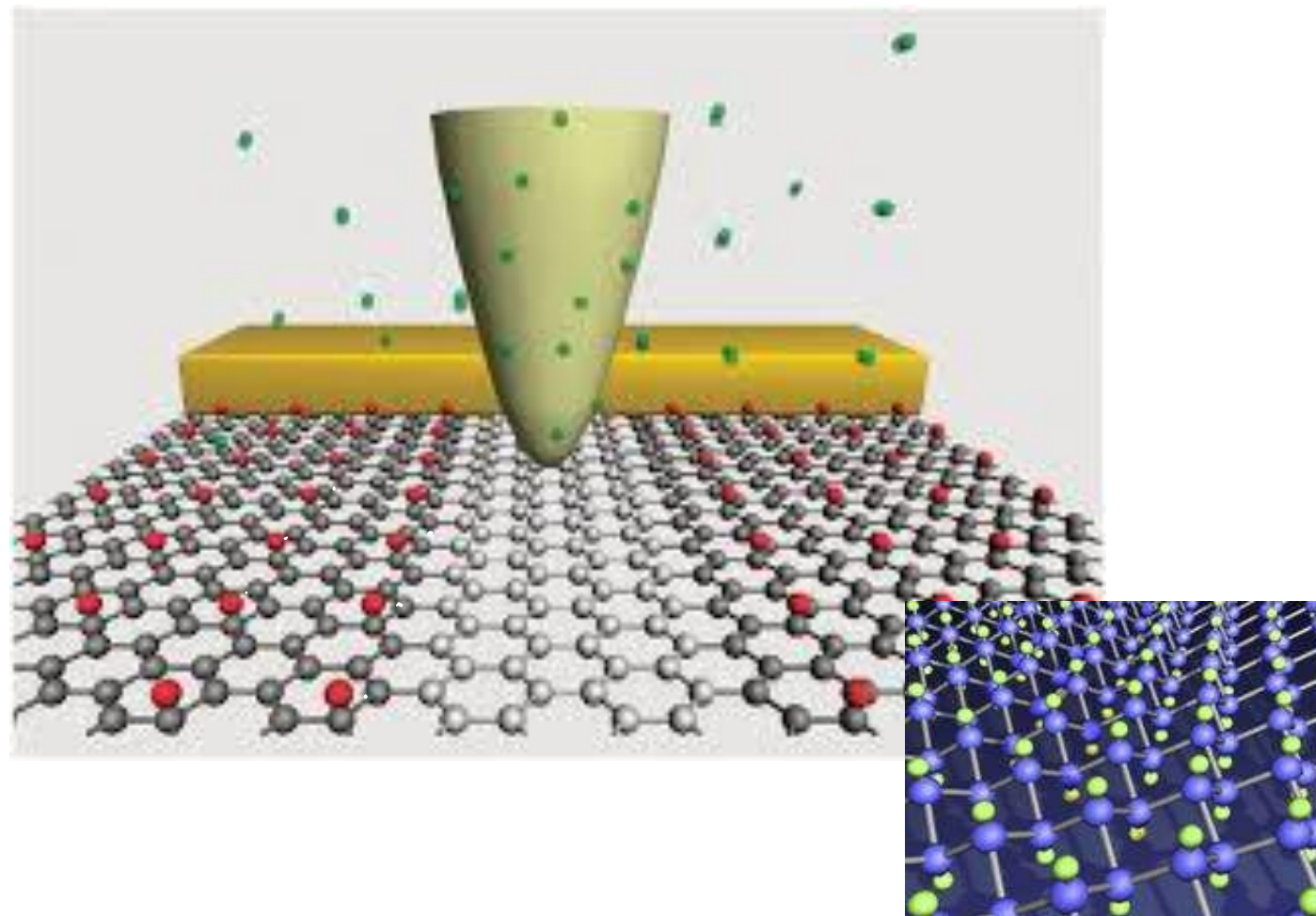


In a 2D material the bulk is a surface, and the surface is an edge

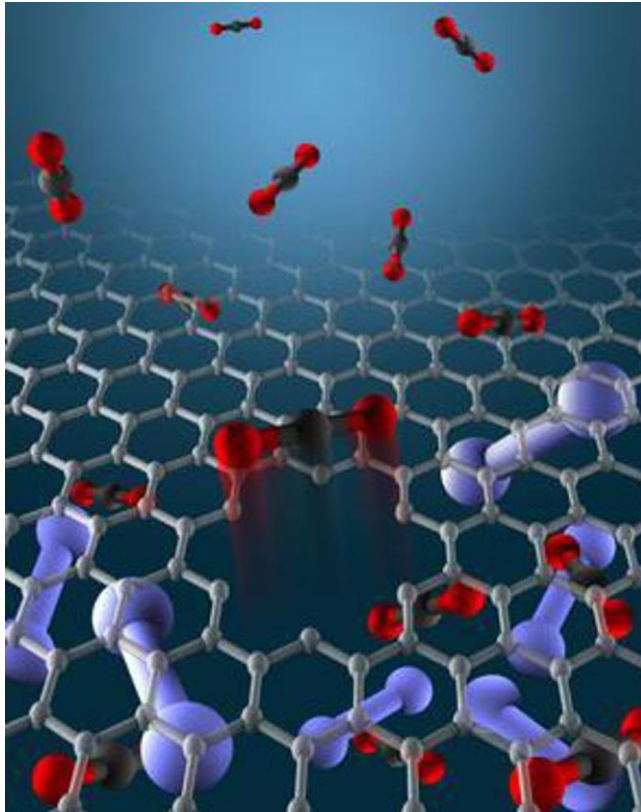
Functionalise 2D material with other molecules



Convert 2D material into another material, and back

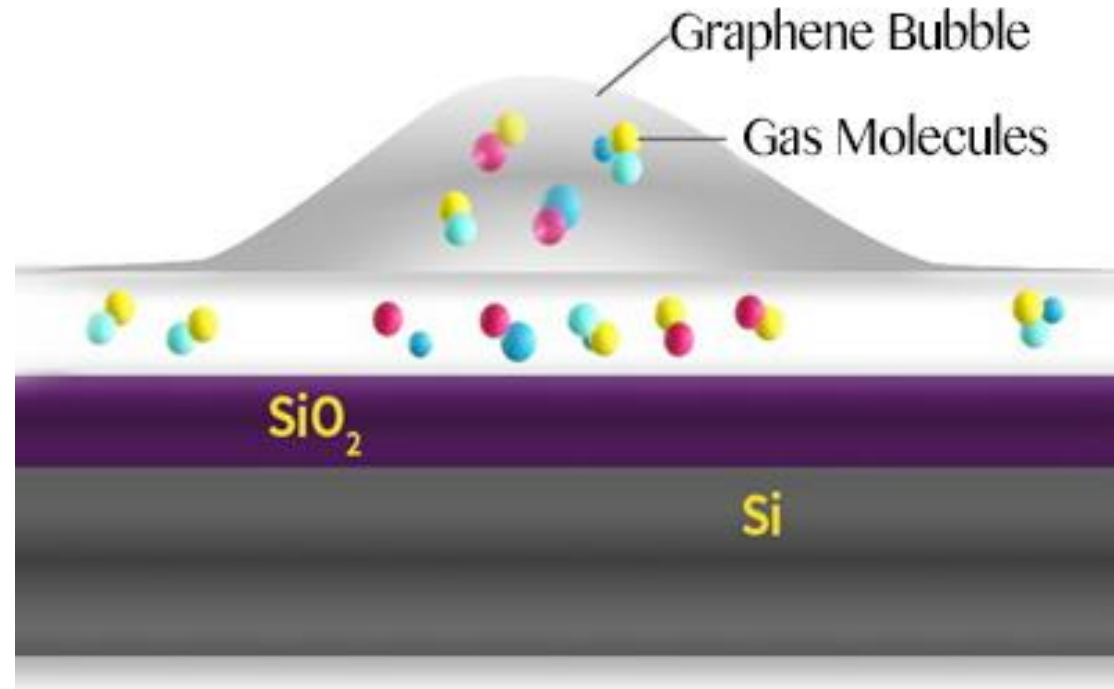


Create holes for ionfilters, molecular sieves, and DNA translocation



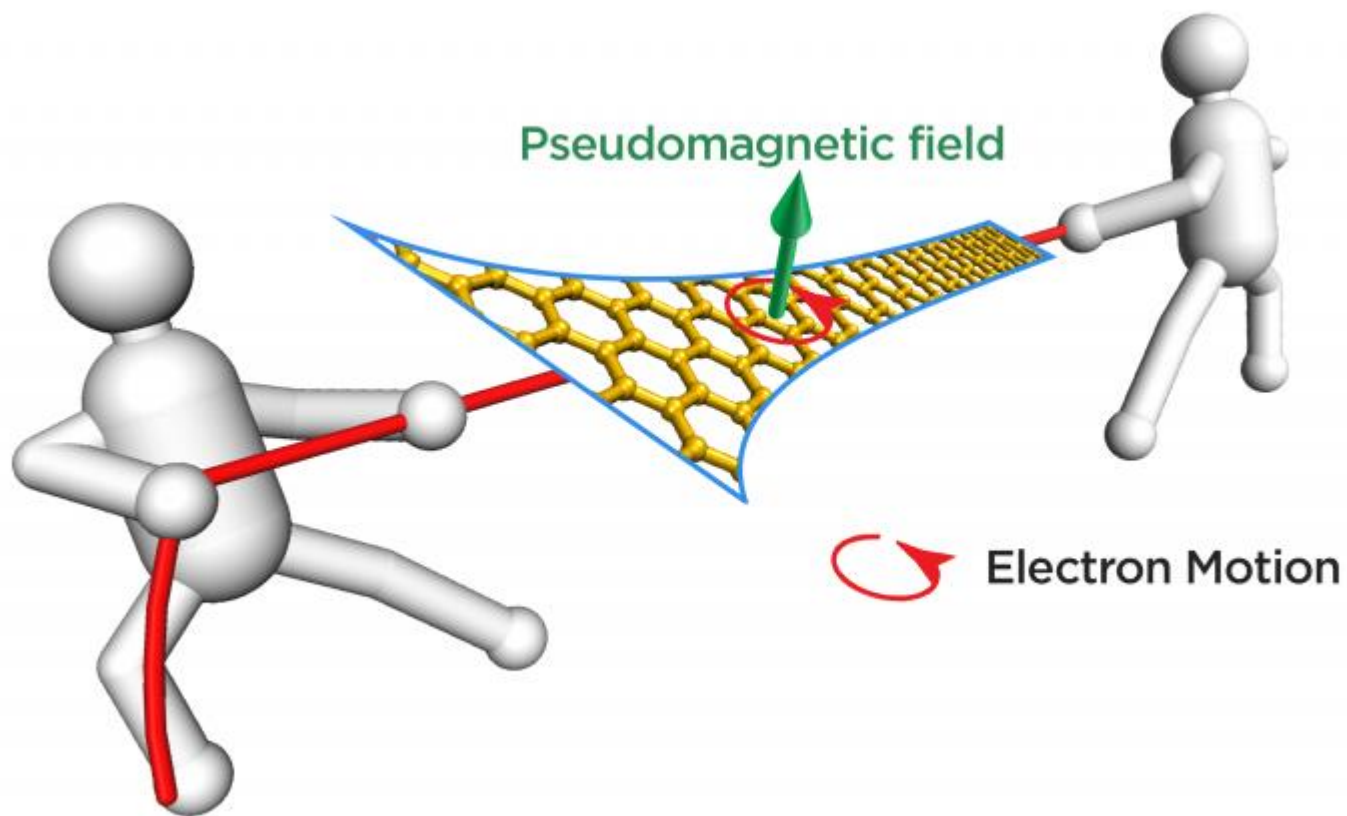
<https://spectrum.ieee.org/graphenebased-gas-membranes-promise-reduced-carbon-dioxide-emissions>

Trap molecules and do chemical reactions inside attoliter cavities, with extreme reaction rates

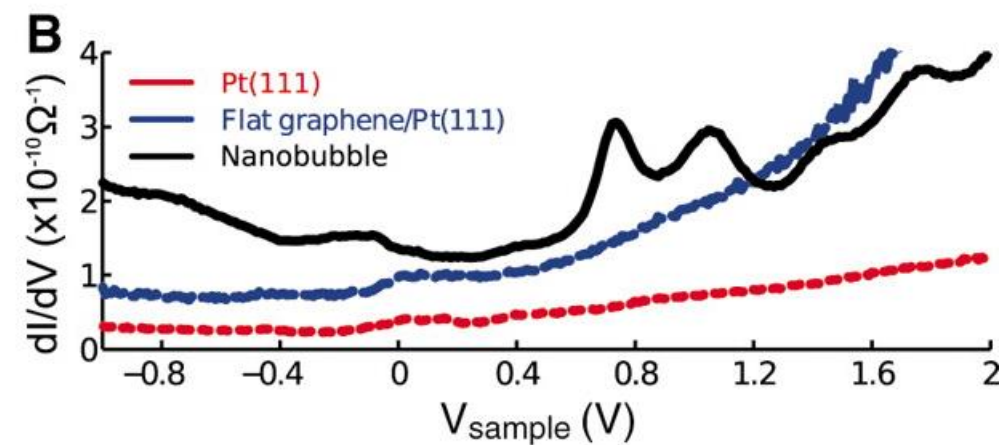
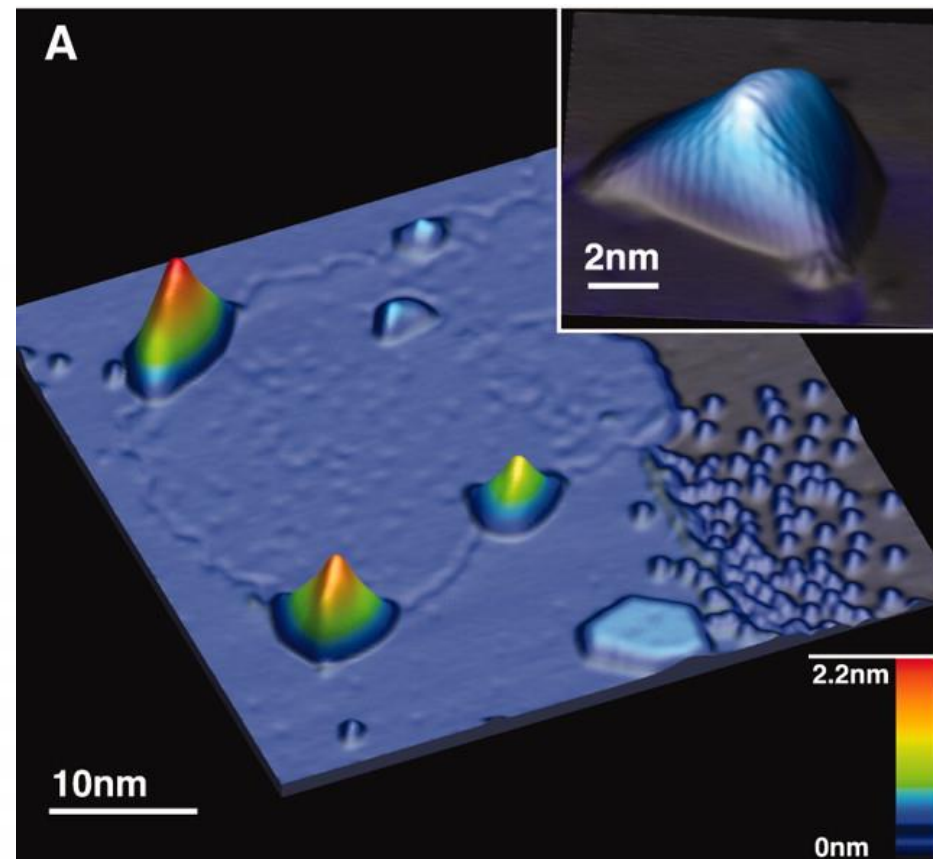


•Yuan Huang, Xiao Wang, Xu Zhang, Xianjue Chen, Baowen Li, Bin Wang, Ming Huang, Chongyang Zhu, Xuewei Zhang, Wolfgang S. Bacsá, Feng Ding, and Rodney S. Ruoff; "Raman Spectral Band Oscillations in Large Graphene Bubbles"; Phys. Rev. Lett.; 2018

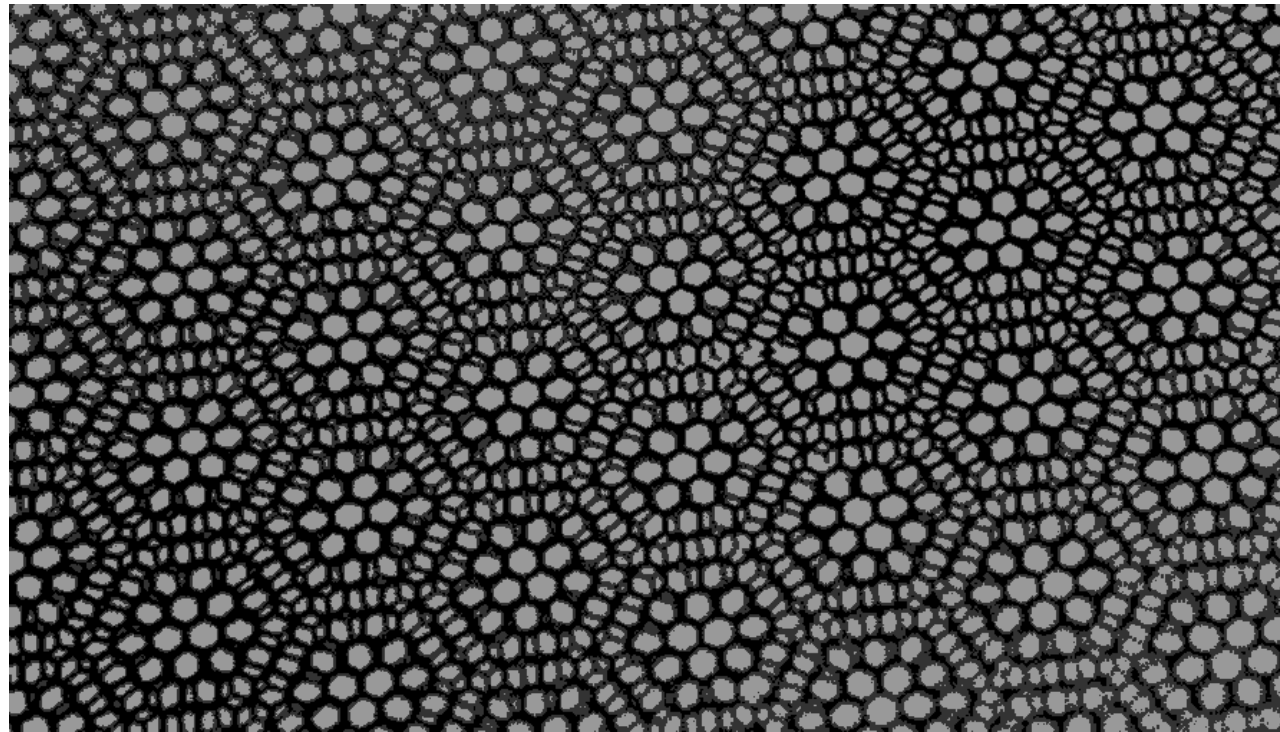
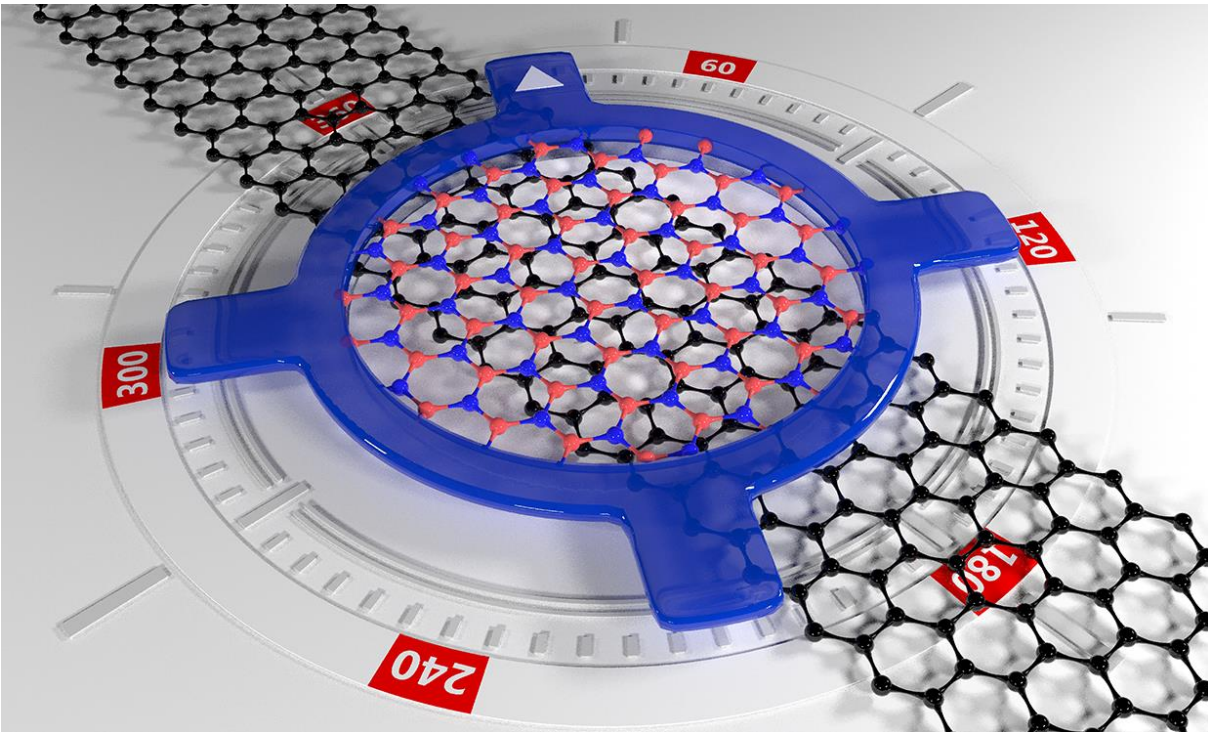
Create strong pseudomagnetic fields by straining graphene



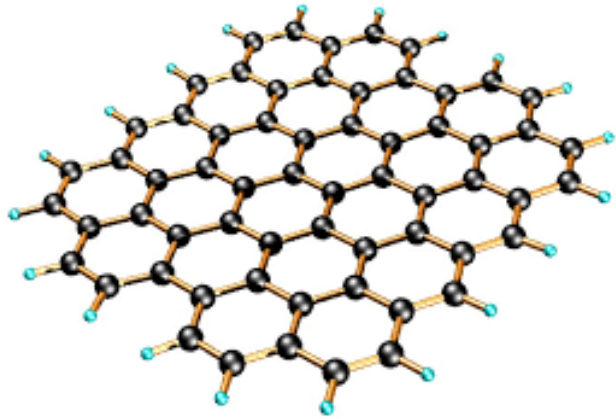
PRL 115, 245501 (2015)



Create new electronic or photonic properties by controlling twist angle between two crystals

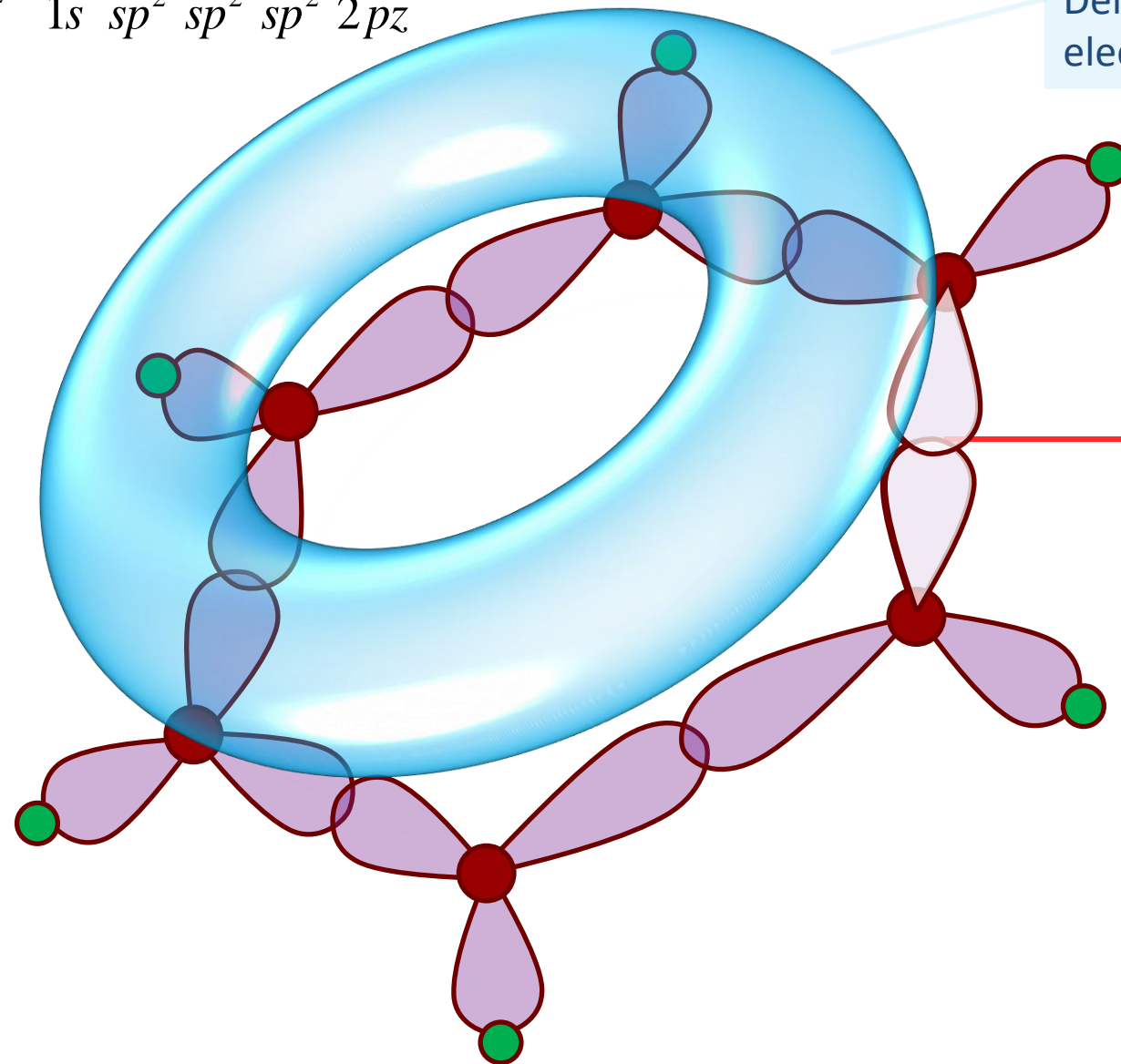
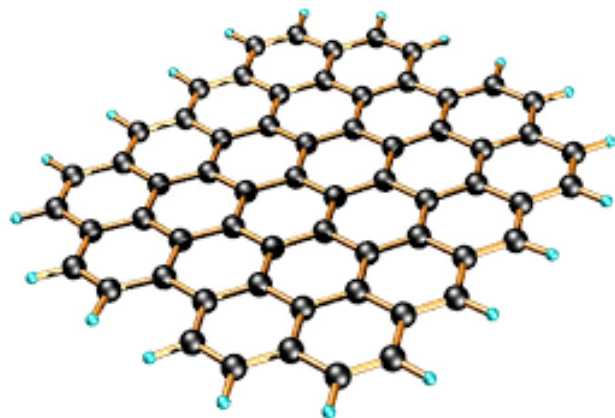
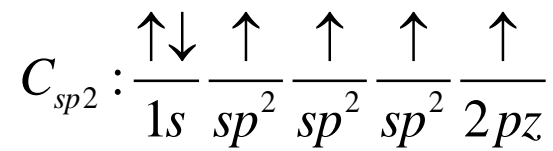


1. What is graphene?



Graphene is a 2D sheet of carbon atoms with record electrical and thermal conductivity, mechanical strength, stability, impermeability.

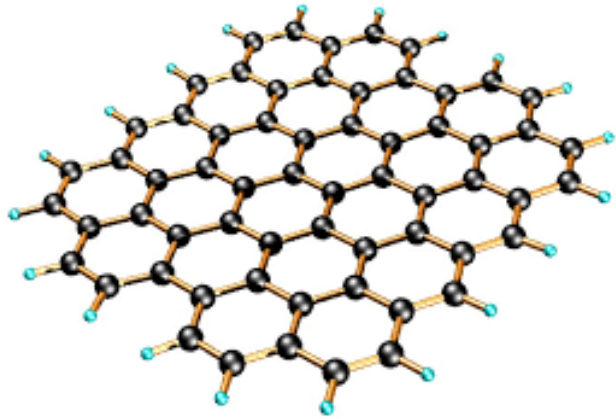




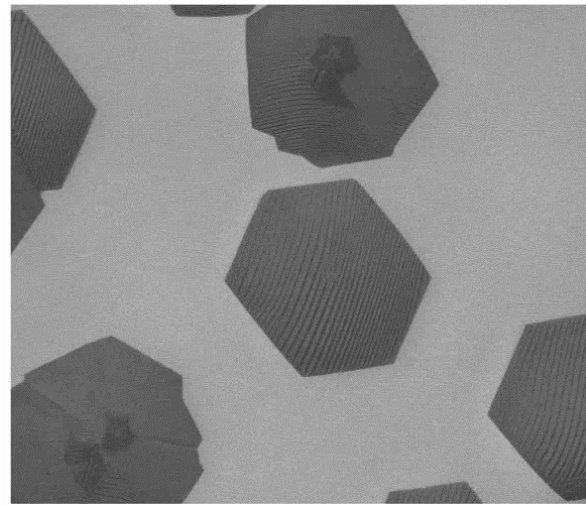
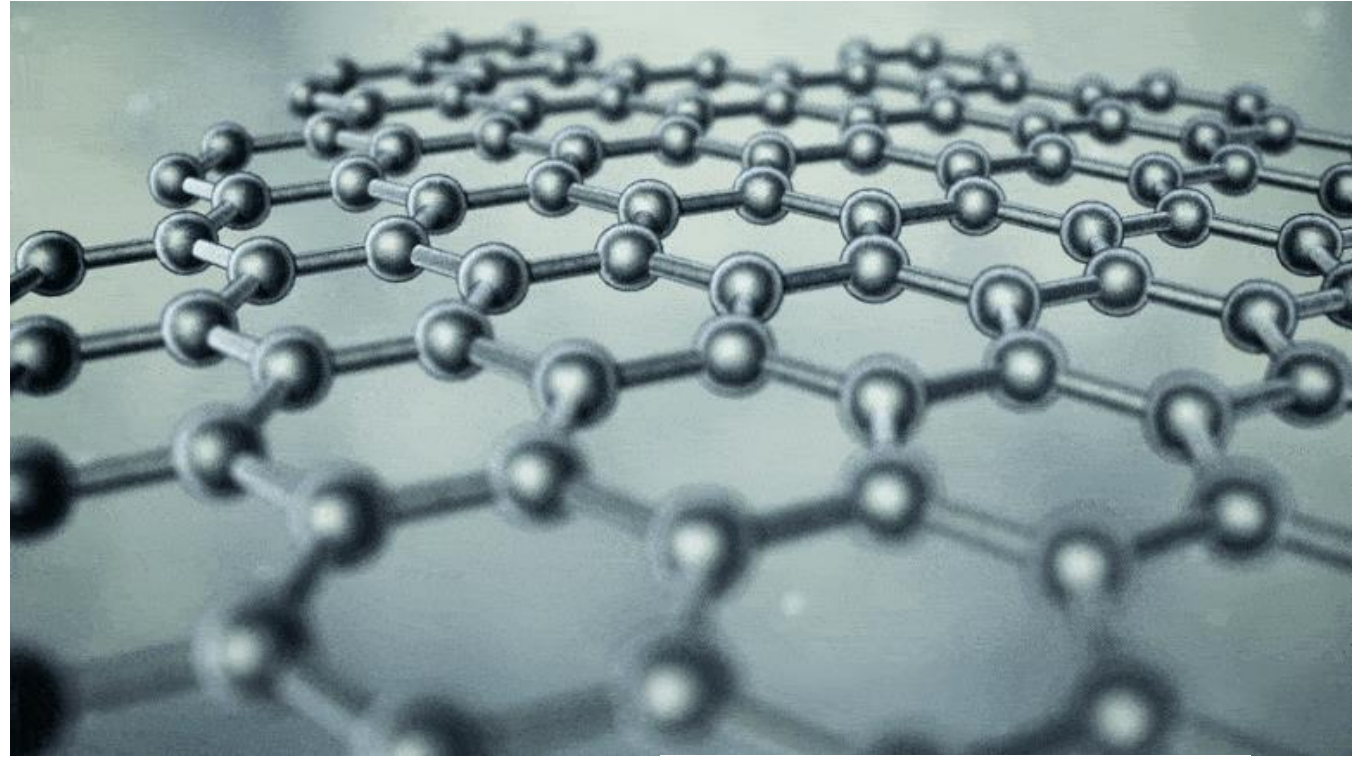
Pi bonds
Delocalised electrons

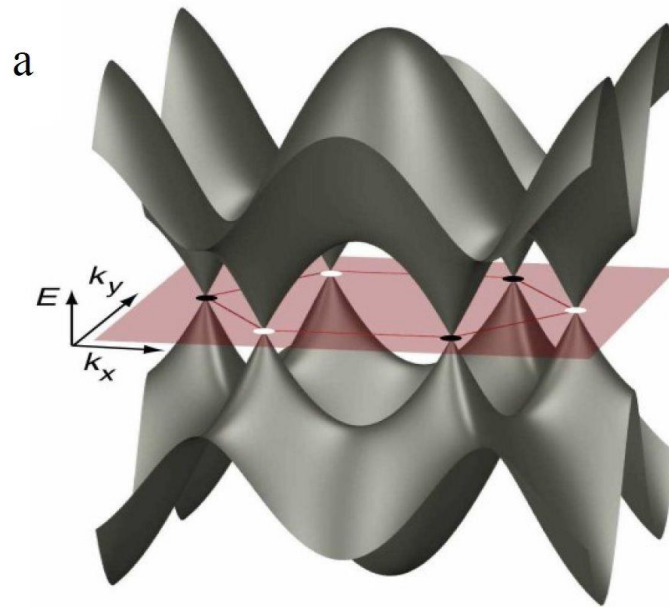
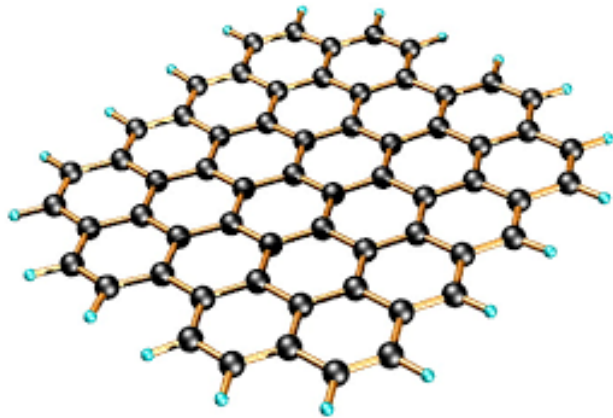
Sigma bonds
Localised electrons

Graphene is a 2D sheet of carbon atoms with record electrical and thermal conductivity, mechanical strength, stability, impermeability.



Graphene is a 2D sheet of carbon atoms with record electrical and thermal conductivity, mechanical strength, stability, impermeability.





Beenakker, Rev Mod Phys, 80 (2008), 1337



Graphene is a 2D sheet of carbon atoms with record electrical and thermal conductivity, mechanical strength, stability, impermeability.

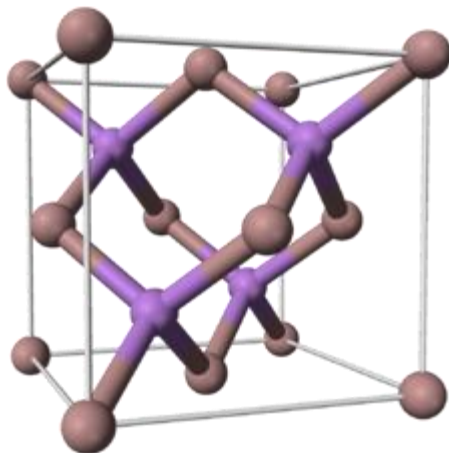
Graphene is a zero-bandgap semiconductor with a linear dispersion :

$$E_F = c \cdot p = v_F \cdot \hbar k_F$$

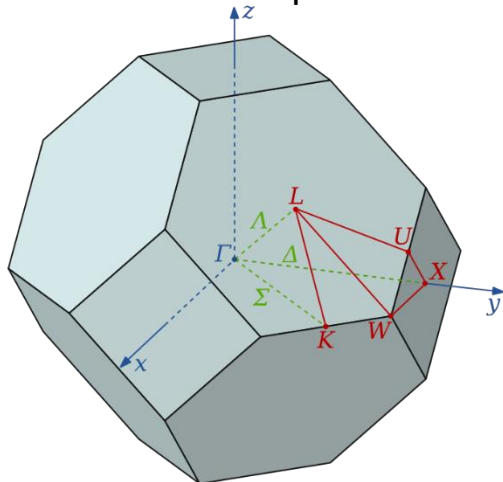
Graphene electrons are massless relativistic quasiparticles, travelling at the "speed of light"

$$v_F = \frac{c}{300}$$

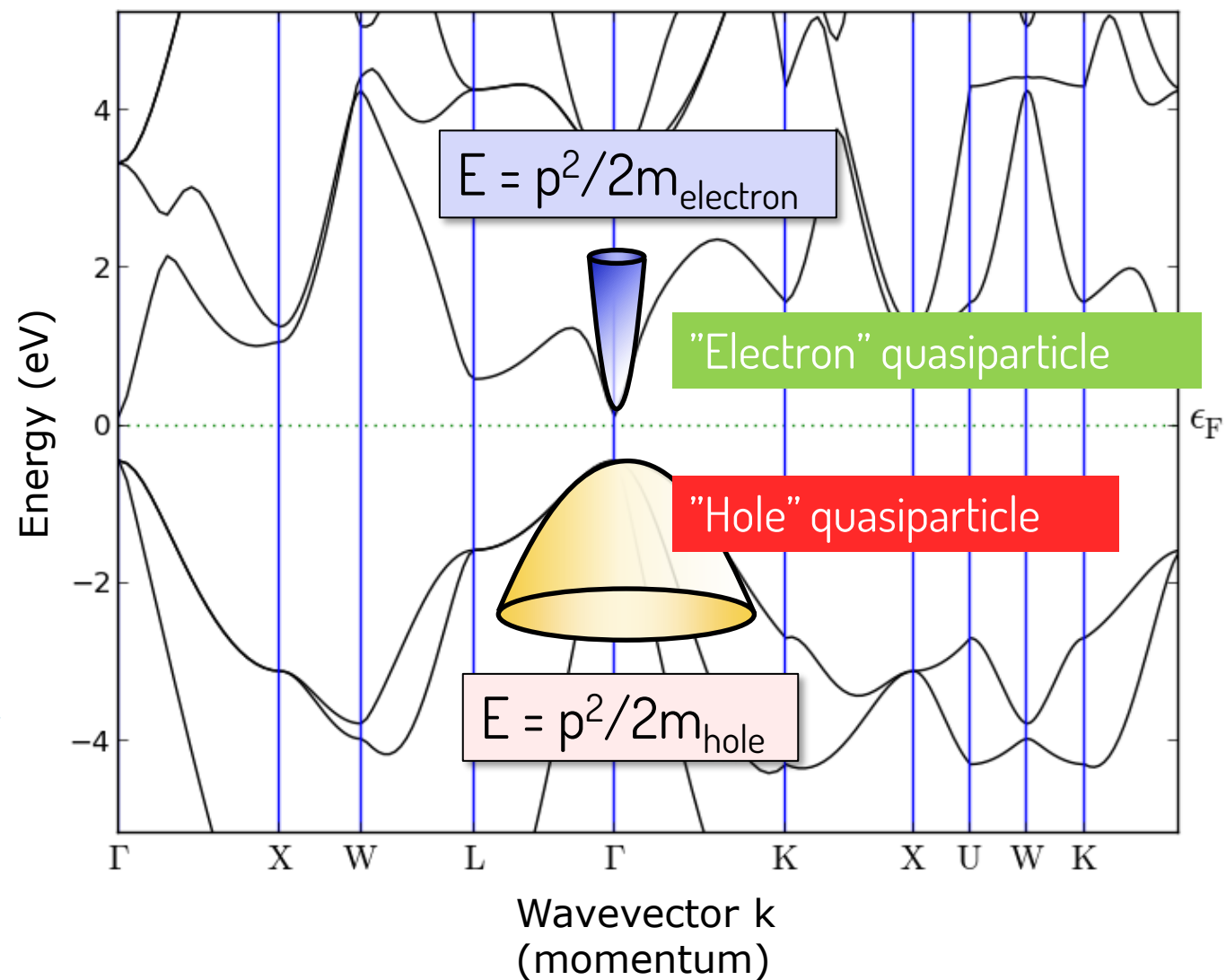
Real space

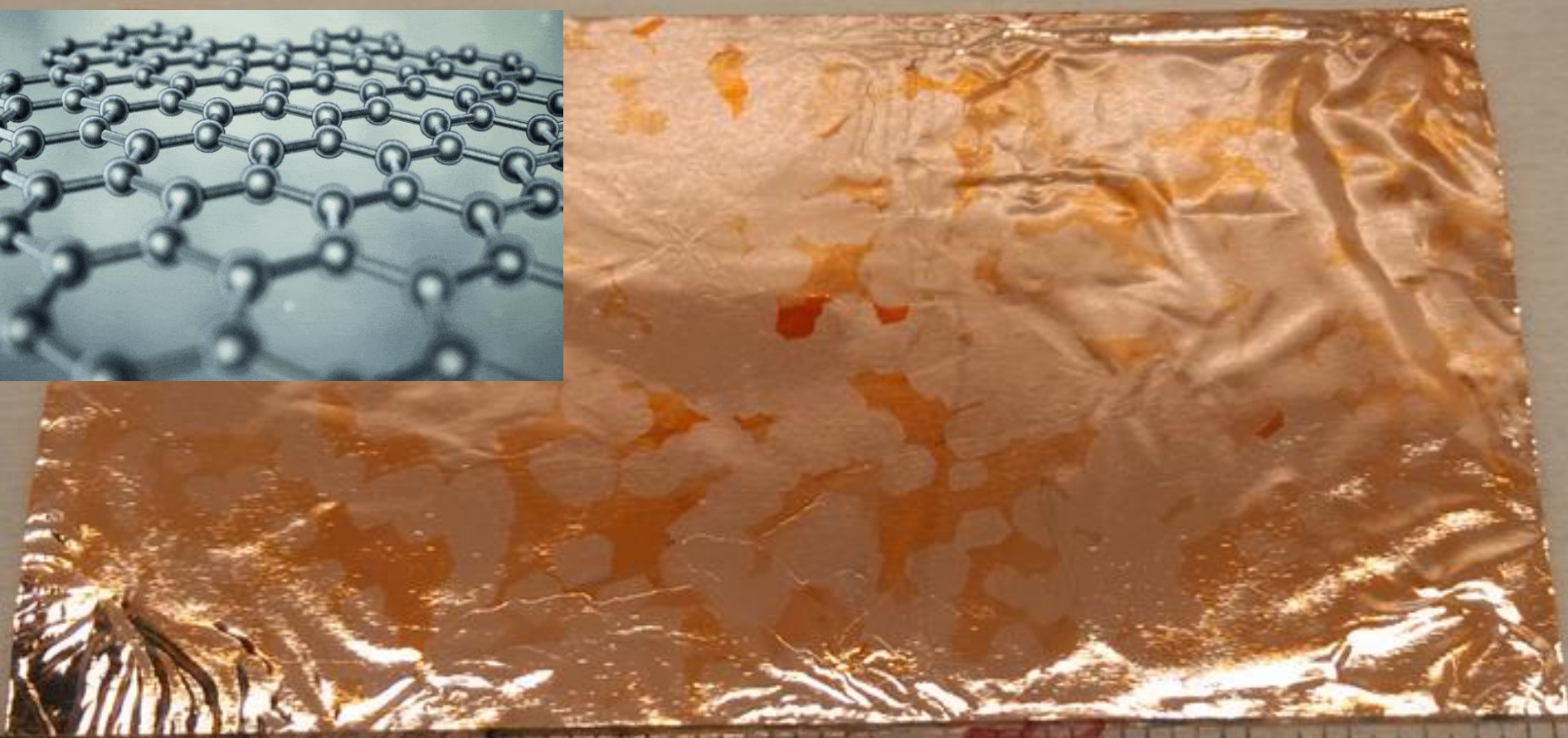
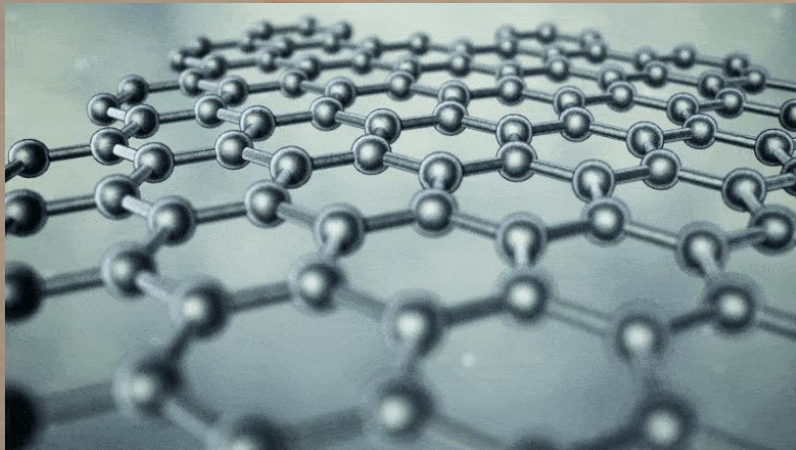


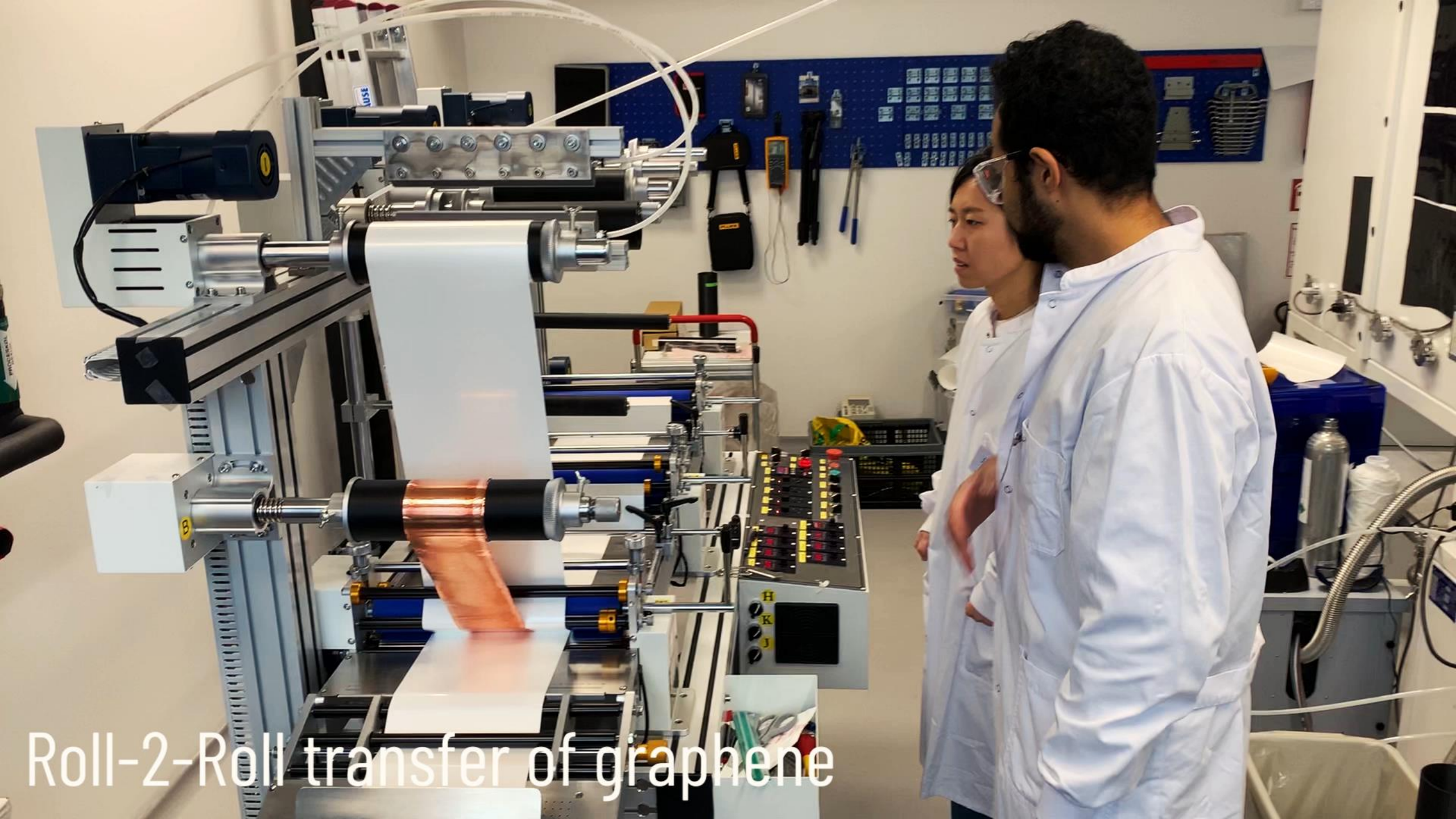
Momentum space



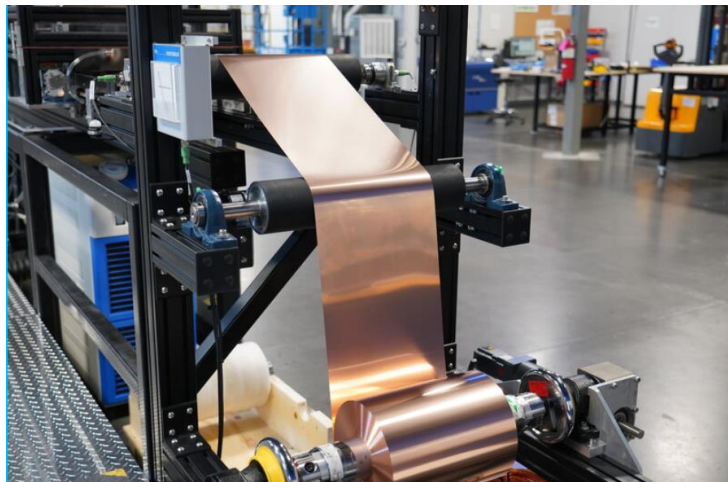
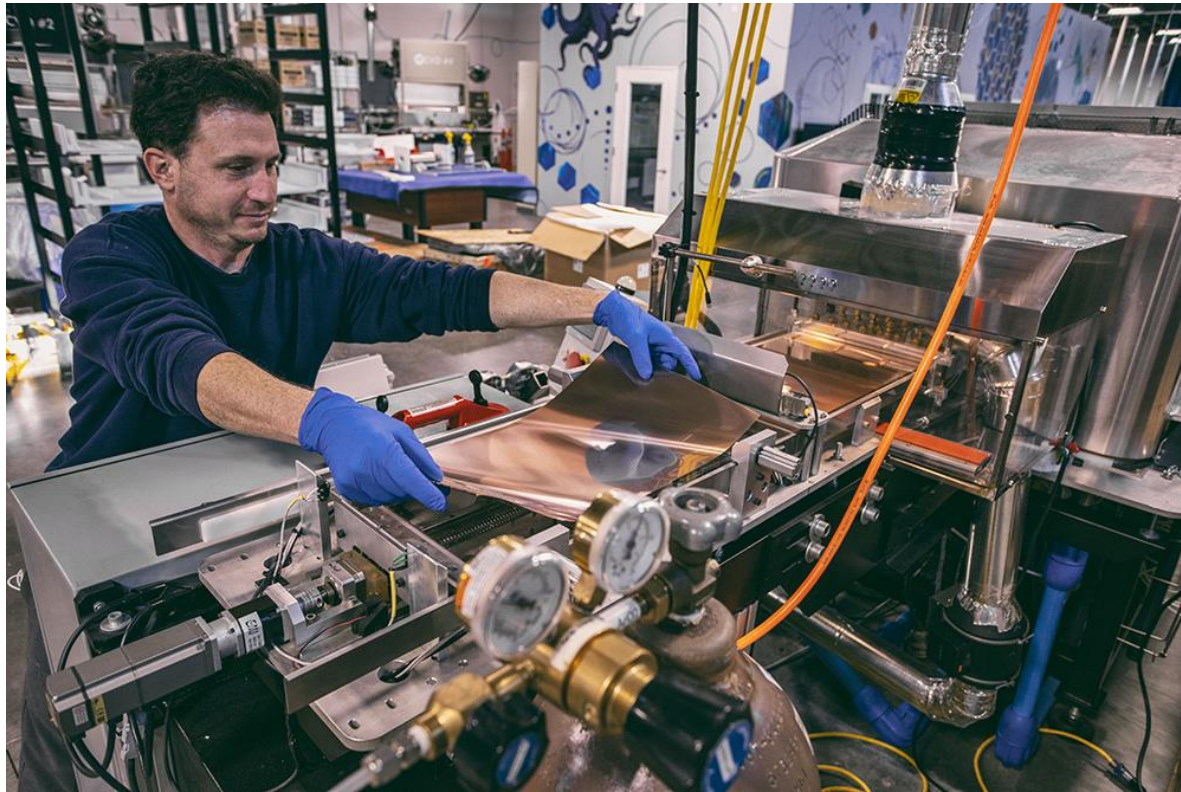
GaAs Bandstructure (from quantumwise.com)



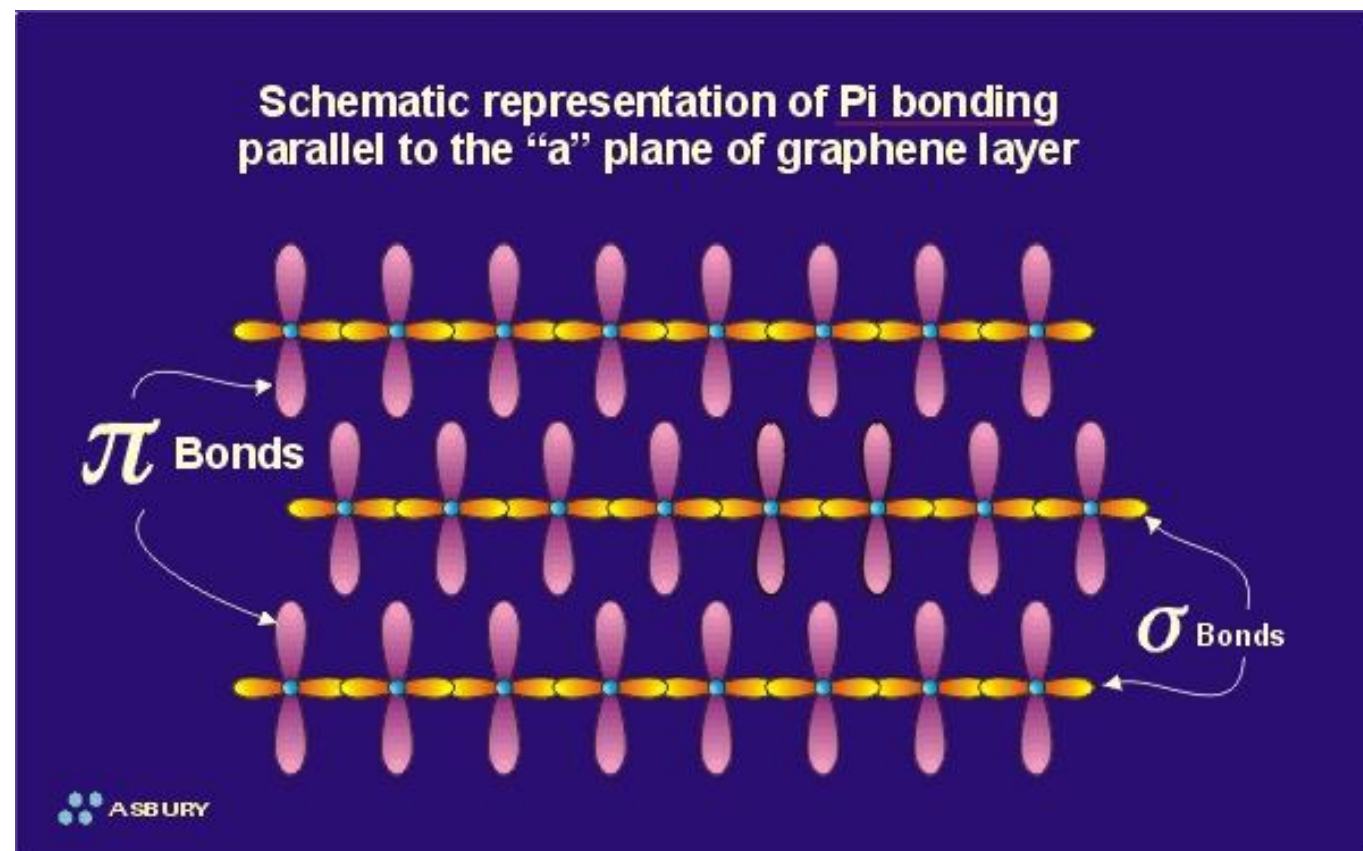
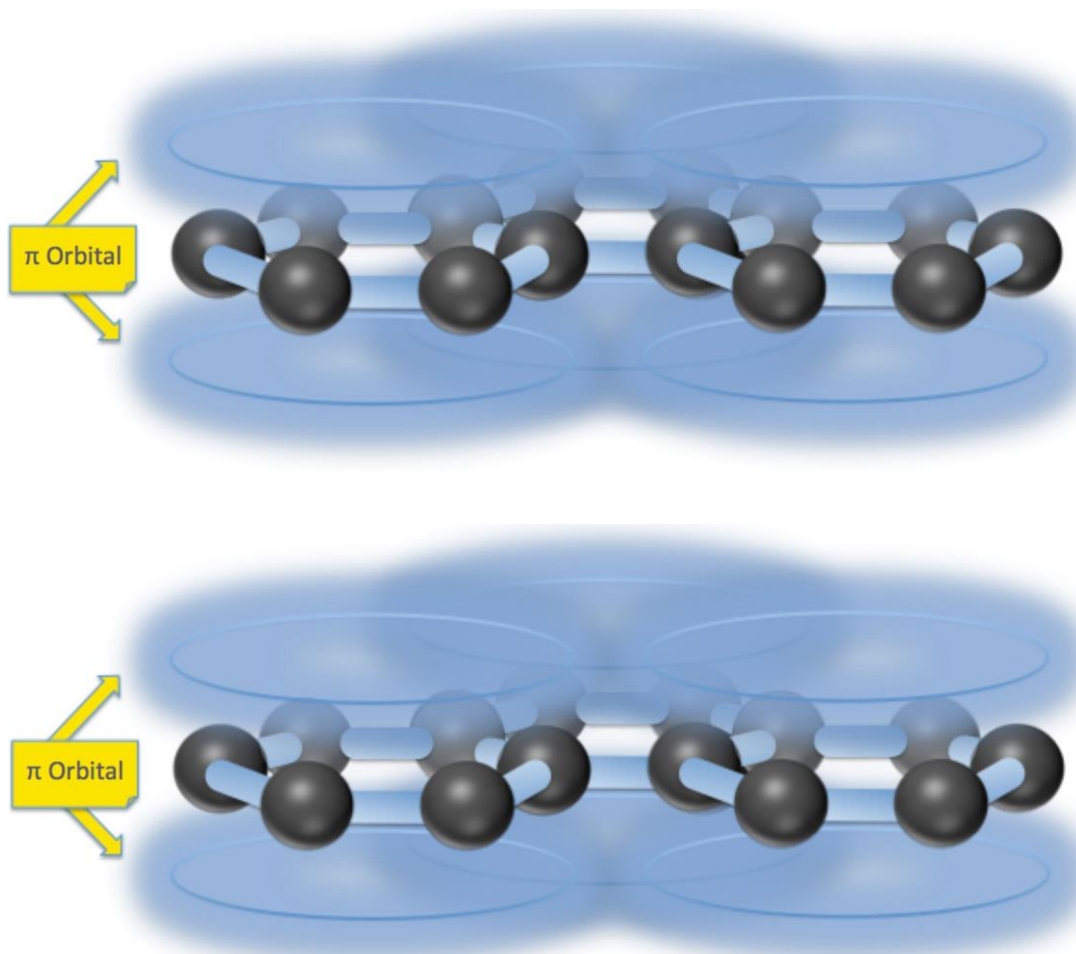




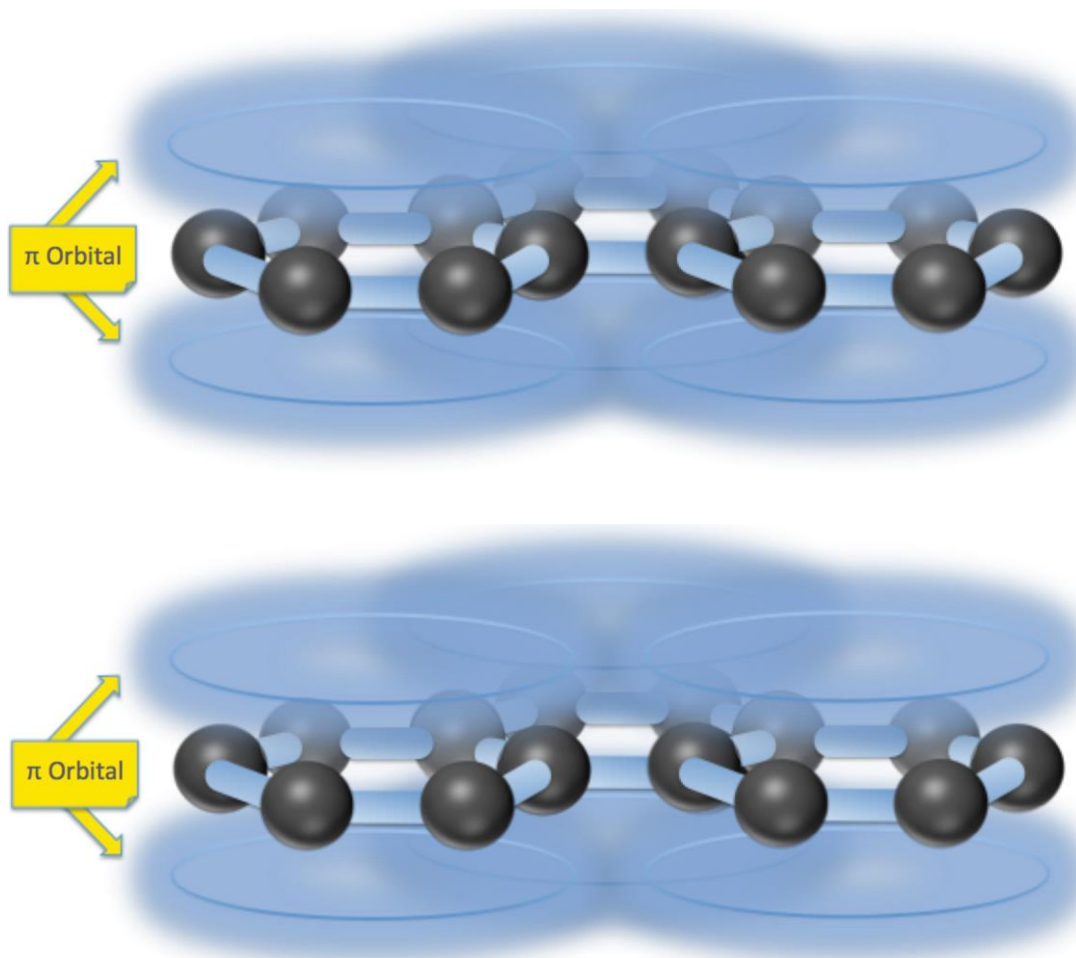
Roll-2-Roll transfer of graphene



2. 2D van der Waals
epitaxy



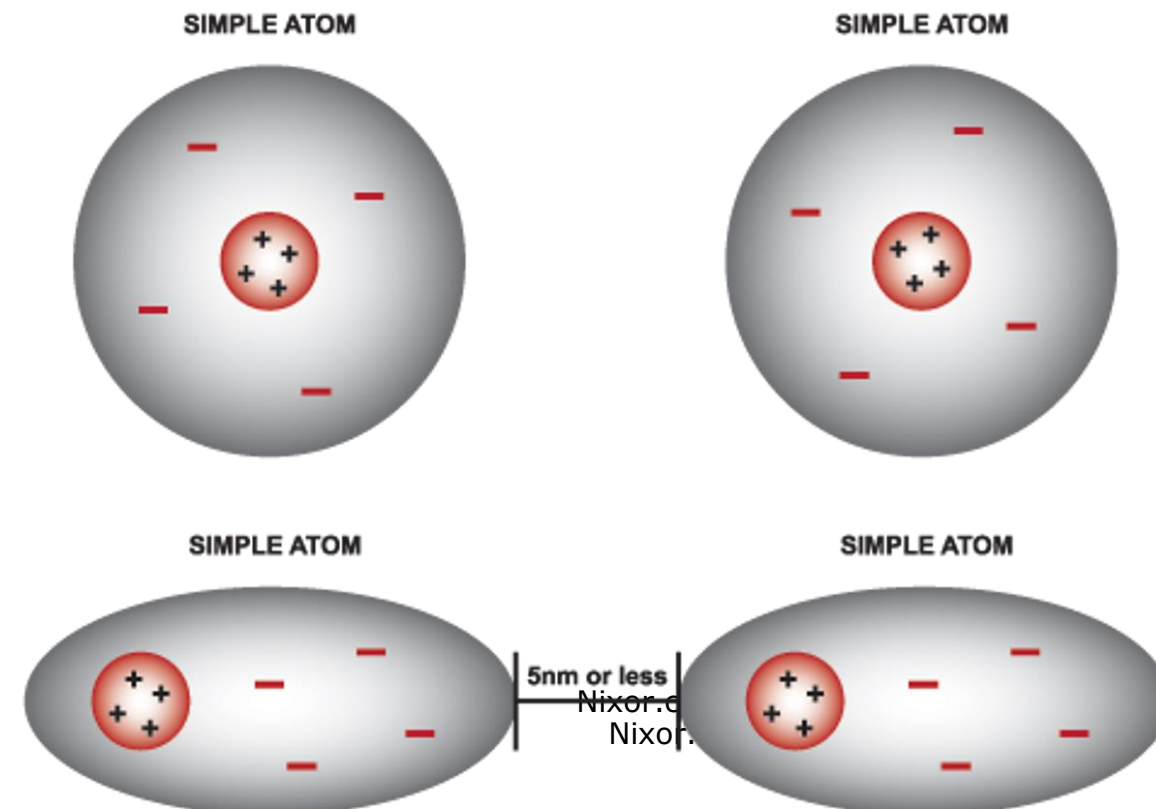
What special properties does graphene have?

VAN DER WAALS' FORCES (VDW)
DIAGRAM

KEY

+ POSITIVE NUCLEUS

- NEGATIVE CHARGED ELECTRON CLOUD

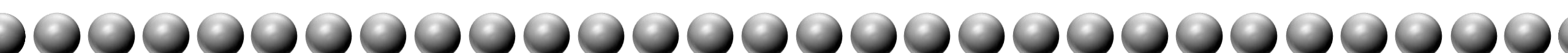
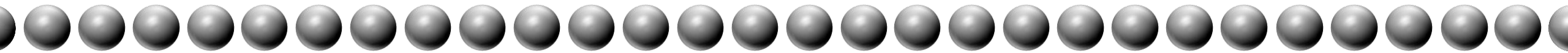


When two atoms come within 5 nanometers of each other, there will be a slight interaction between them, thus causing polarity and a slight attraction.

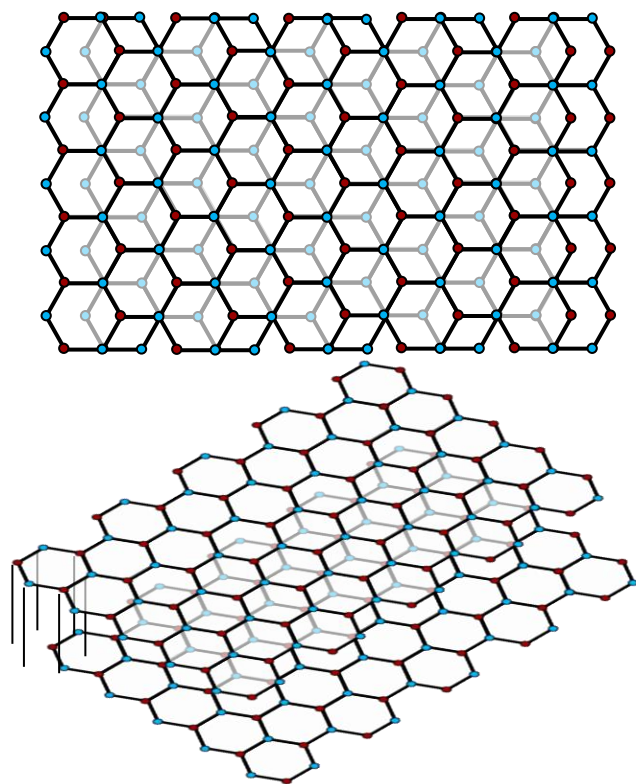
$$W_{ab} = -\frac{C_{orient} + C_{ind} + C_{disp}}{r^6} = -\frac{C}{r^6}$$

$$W_{AB} = \sum_{i,j} \frac{C_{vdW}}{r_{ij}^6}$$

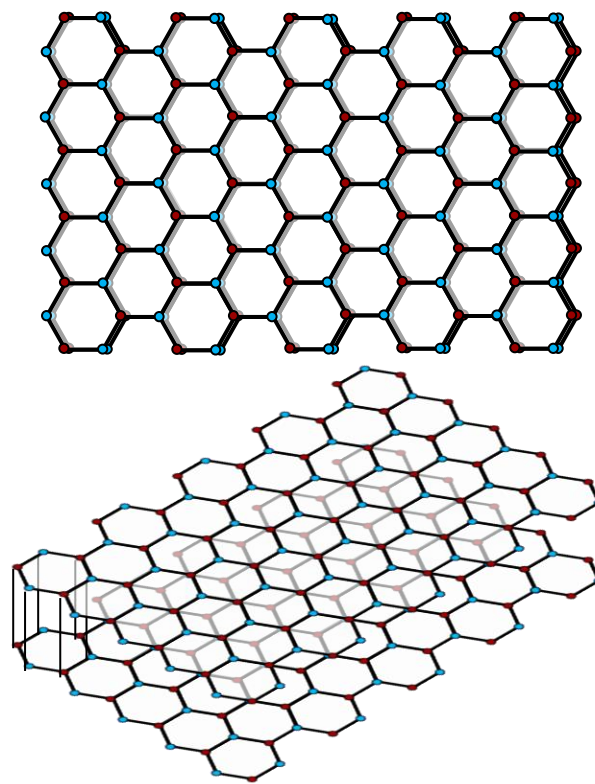
$$W_{AB} = -\frac{C_{ab}}{r_{ab}^6} \cdot dV_A \rho_A \cdot dV_B \rho_B$$



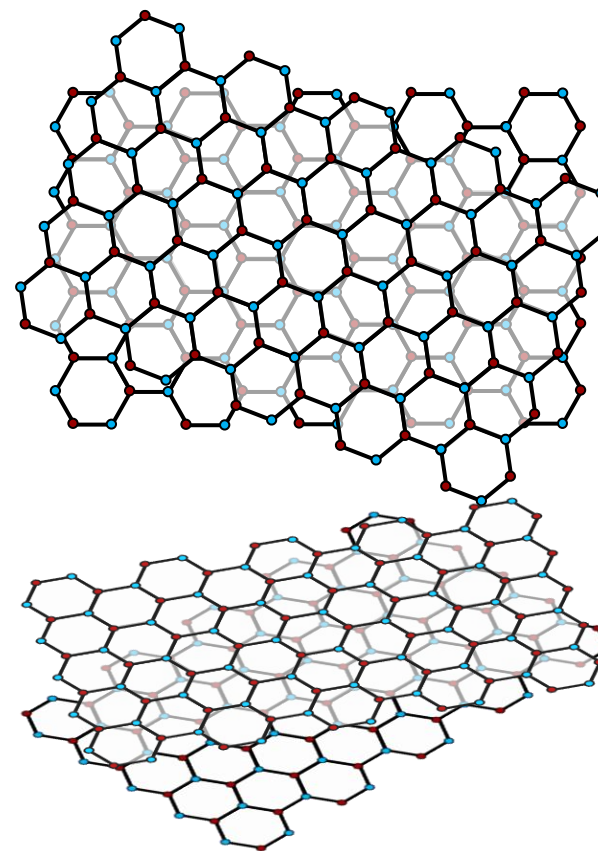
AB stacked

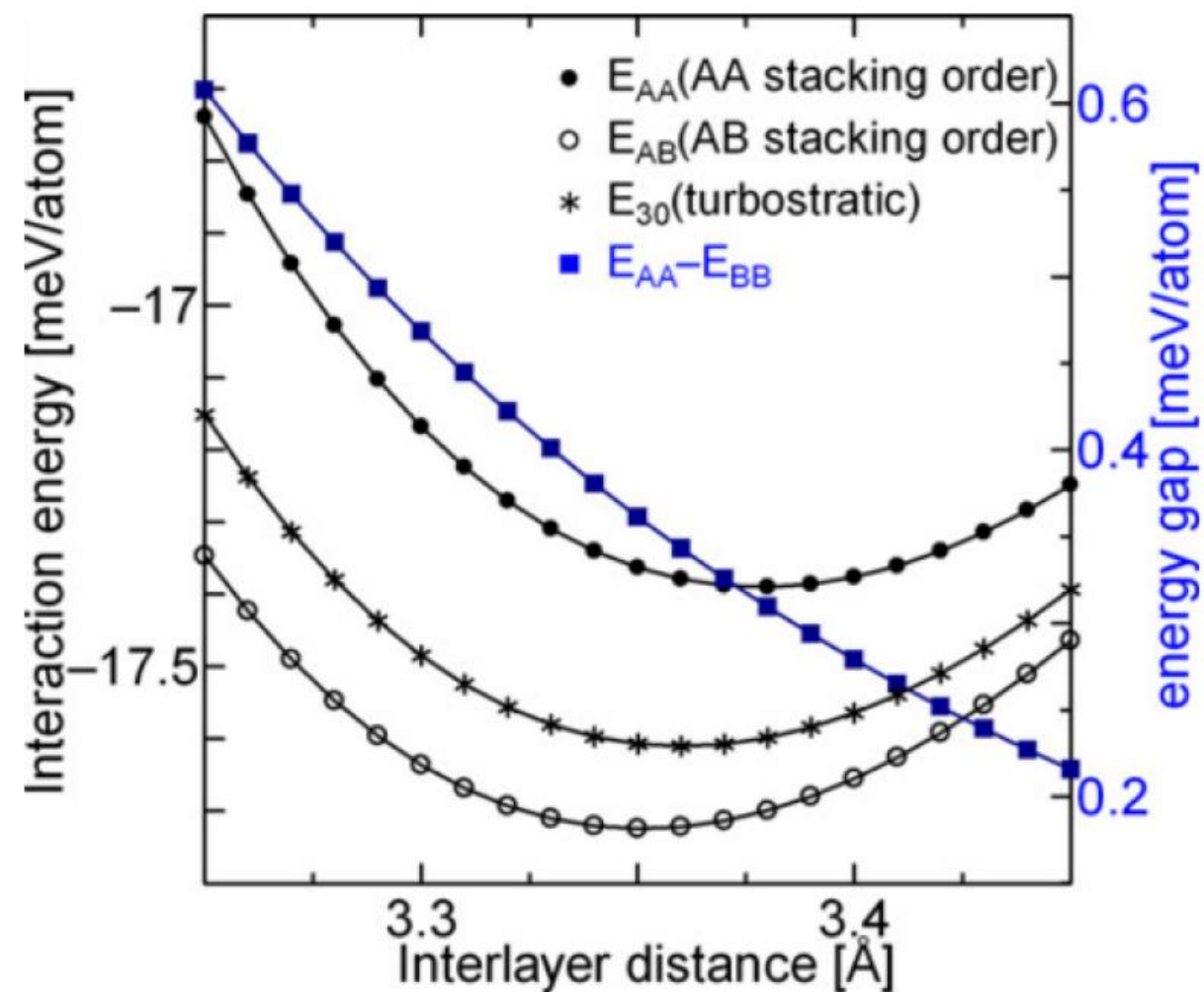
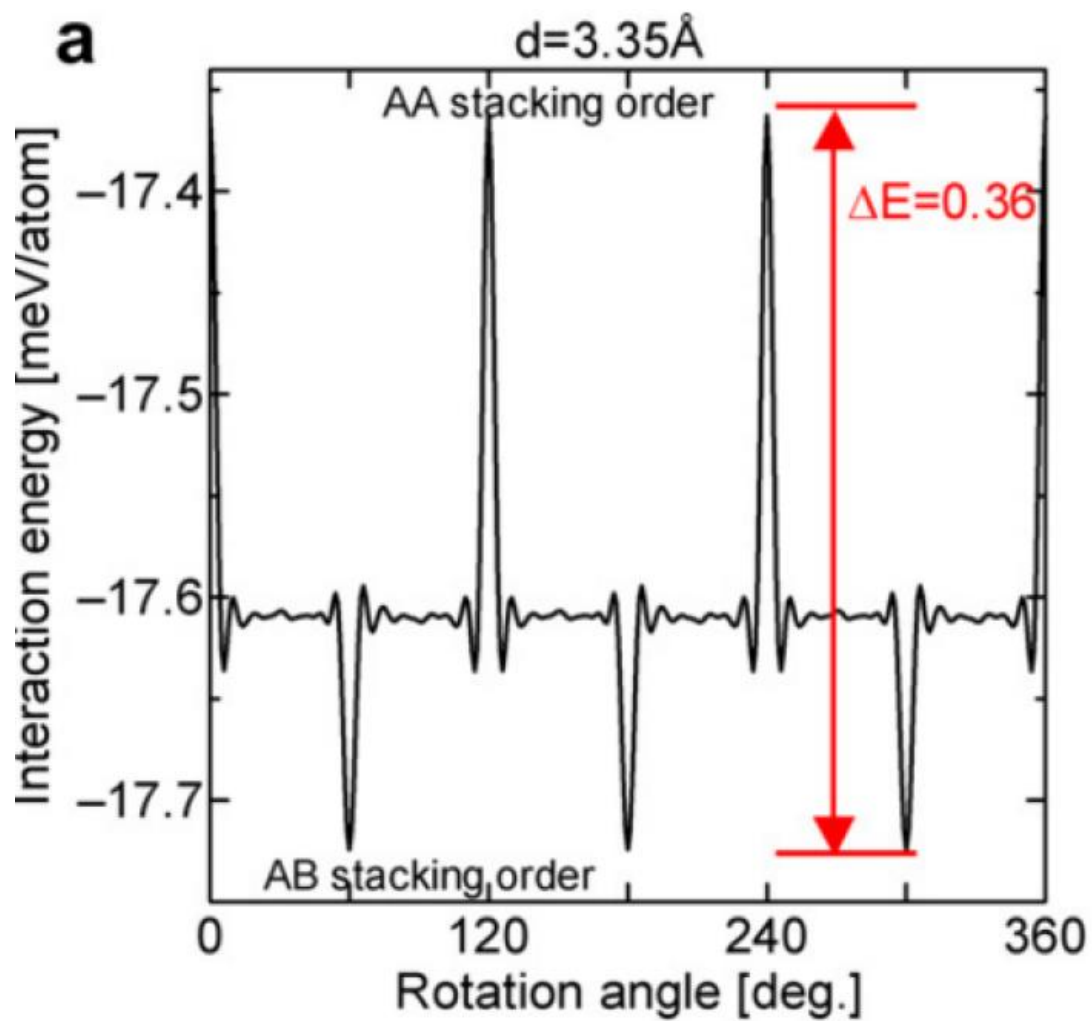


AA stacked



Turbostratic/Twisted

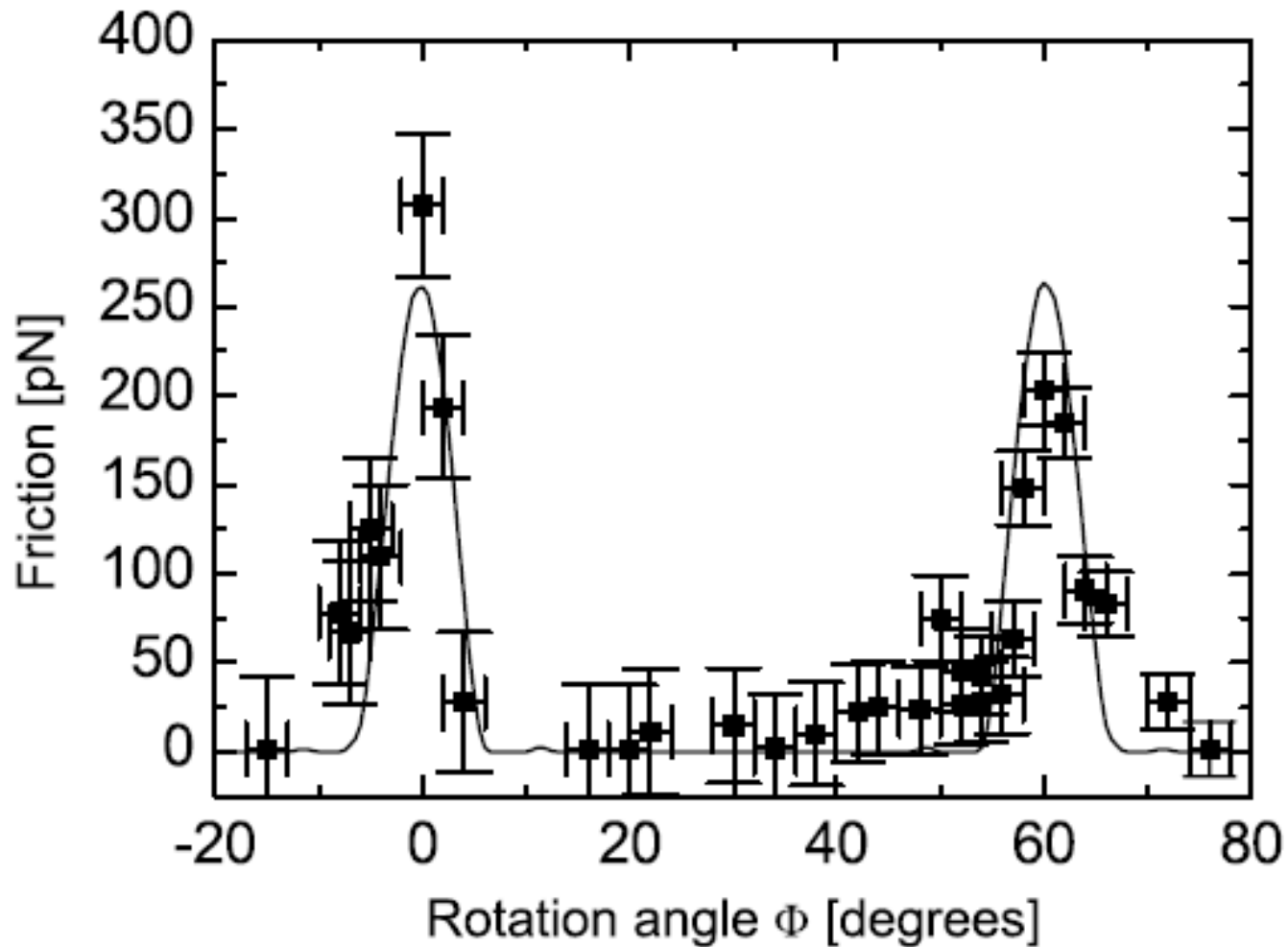




Chemical Physics Letters **2011**, 512 (4-6), 146-150.

Superlubricity of Graphite

Martin Dienwiebel,* Gertjan S. Verhoeven, Nambodiri Pradeep, and Joost W. M. Frenken†
Kamerlingh Onnes Laboratory, Leiden University, P.O. Box 9504, 2300 RA Leiden, The Netherlands



Resistivity of Rotated Graphite–Graphene Contacts

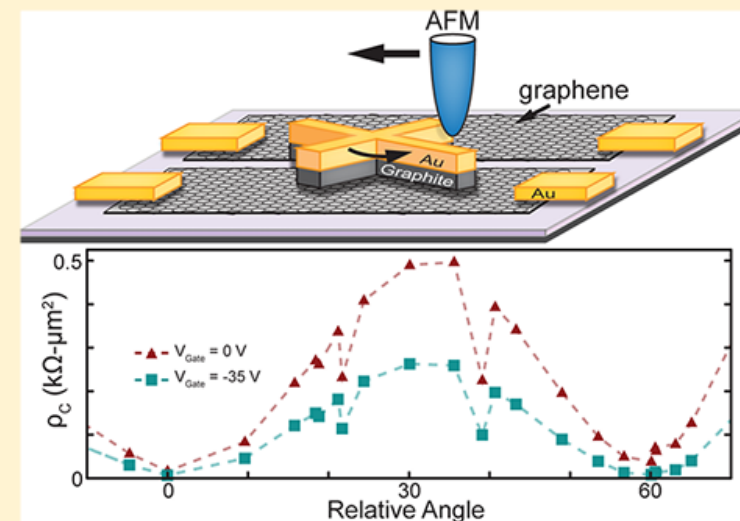
Tarun Chari,[†] Rebeca Ribeiro-Palau,[‡] Cory R. Dean,[‡] and Kenneth Shepard^{*,†}

[†]Department of Electrical Engineering and [‡]Department of Physics, Columbia University, New York, New York 10027, United States

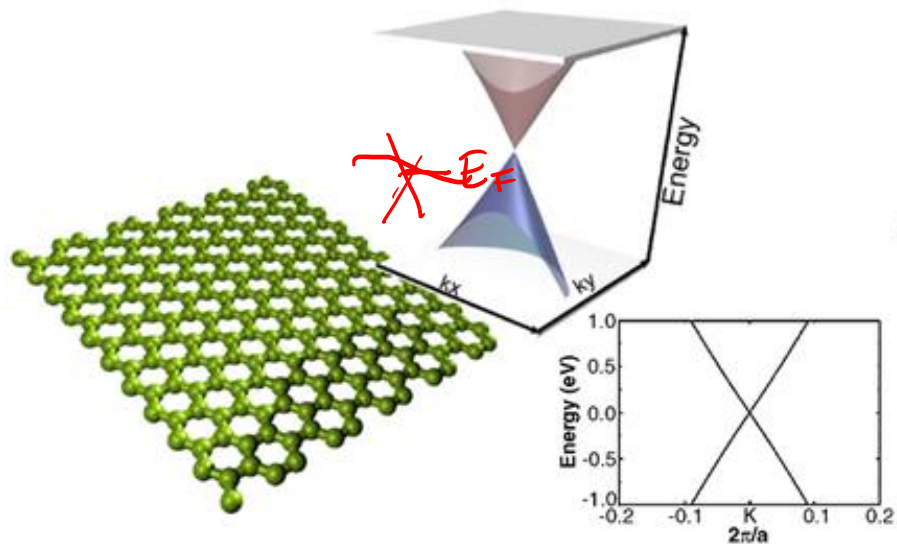
S Supporting Information

ABSTRACT: Robust electrical contact of bulk conductors to two-dimensional (2D) material, such as graphene, is critical to the use of these 2D materials in practical electronic devices. Typical metallic contacts to graphene, whether edge or areal, yield a resistivity of no better than $100 \Omega \mu\text{m}$ but are typically $>10 \text{ k}\Omega \mu\text{m}$. In this Letter, we employ single-crystal graphite for the bulk contact to graphene instead of conventional metals. The graphite contacts exhibit a transfer length up to four-times longer than in conventional metallic contacts. Furthermore, we are able to drive the contact resistivity to as little as $6.6 \Omega \mu\text{m}^2$ by tuning the relative orientation of the graphite and graphene crystals. We find that the contact resistivity exhibits a 60° periodicity corresponding to crystal symmetry with additional sharp decreases around 22° and 39° , which are among the commensurate angles of twisted bilayer graphene.

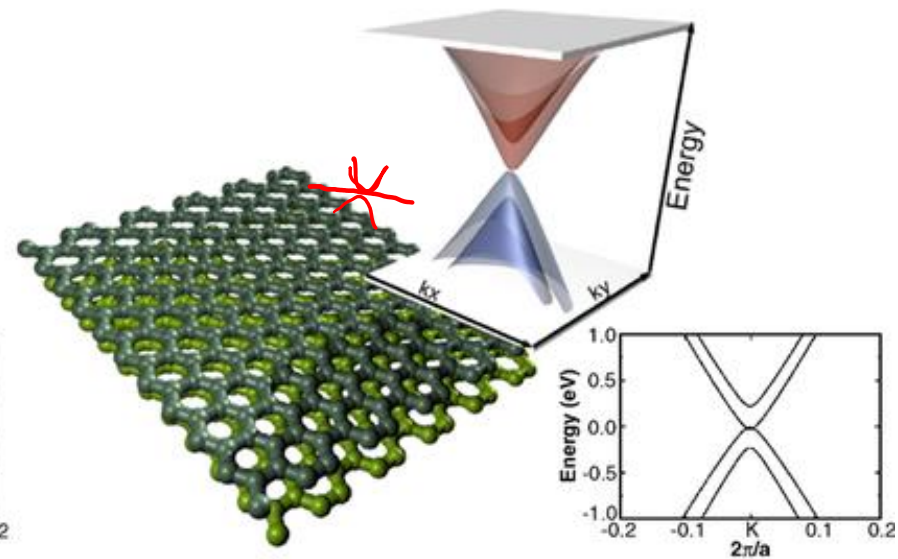
KEYWORDS: Graphene, graphite, contact resistivity, commensurate angles



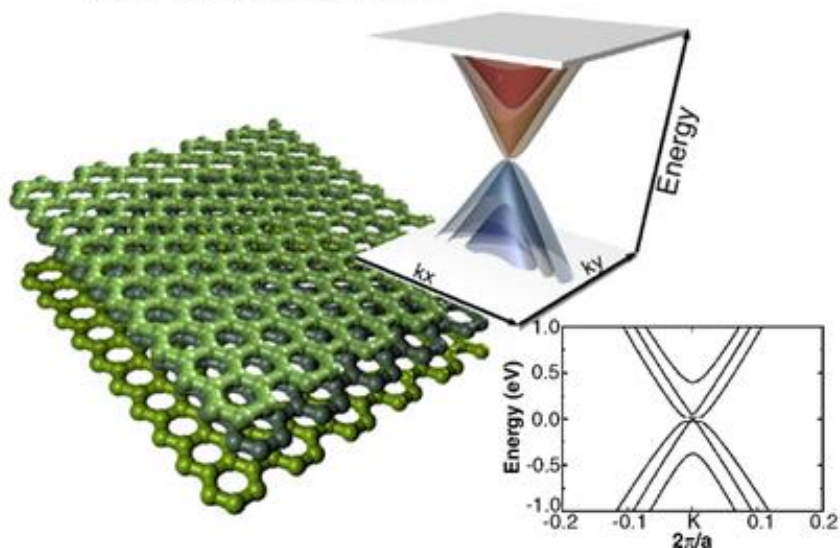
(a) Graphene



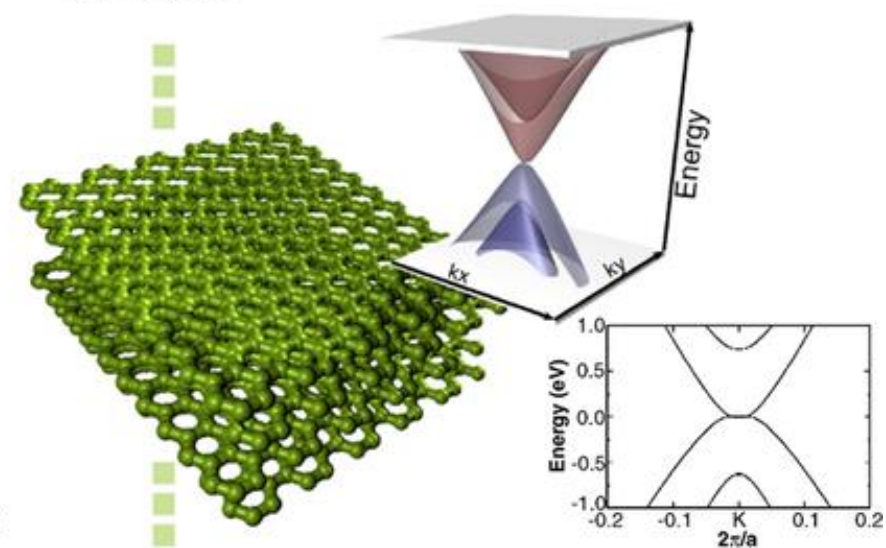
(b) Bi-layer Graphene

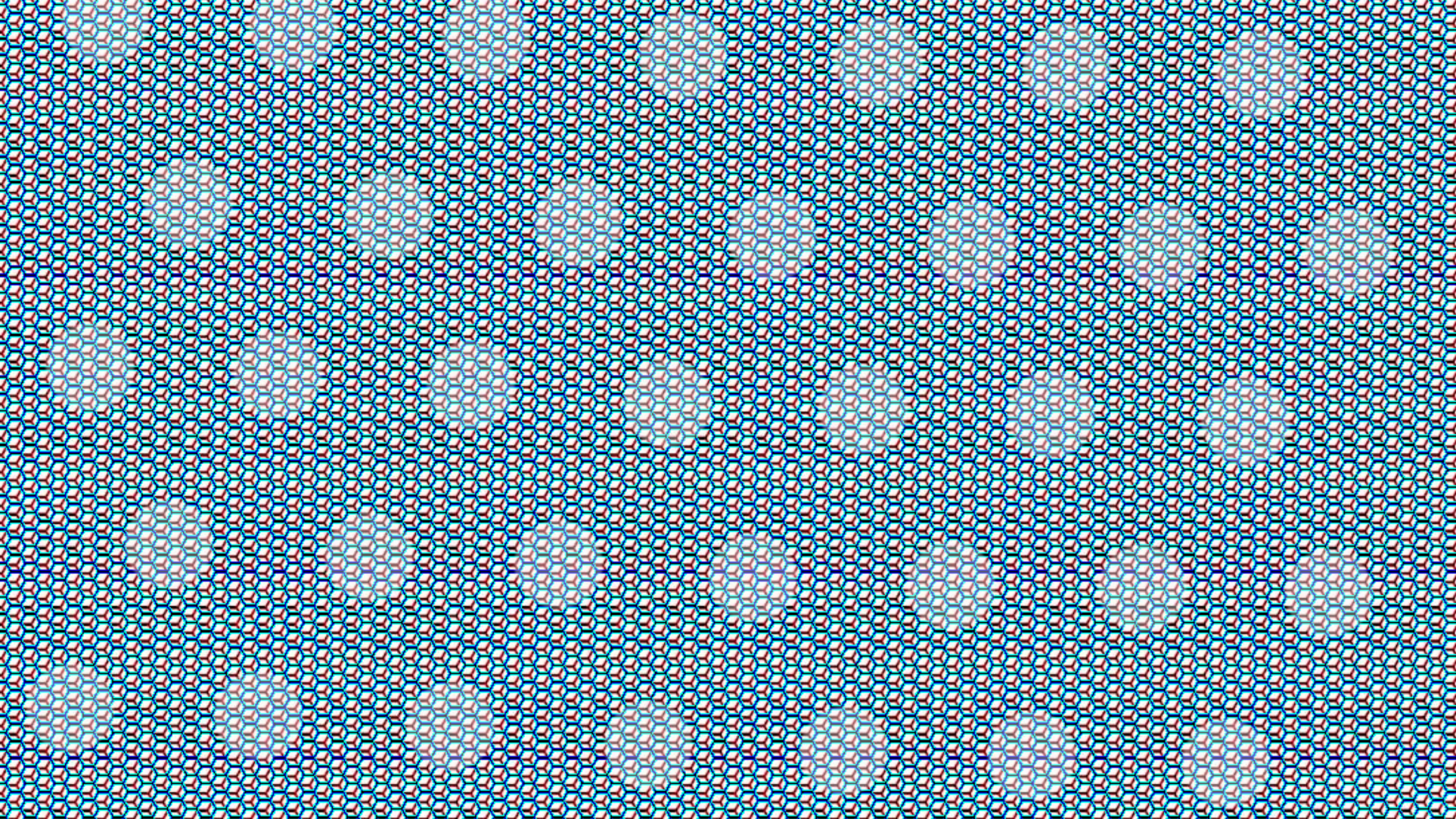


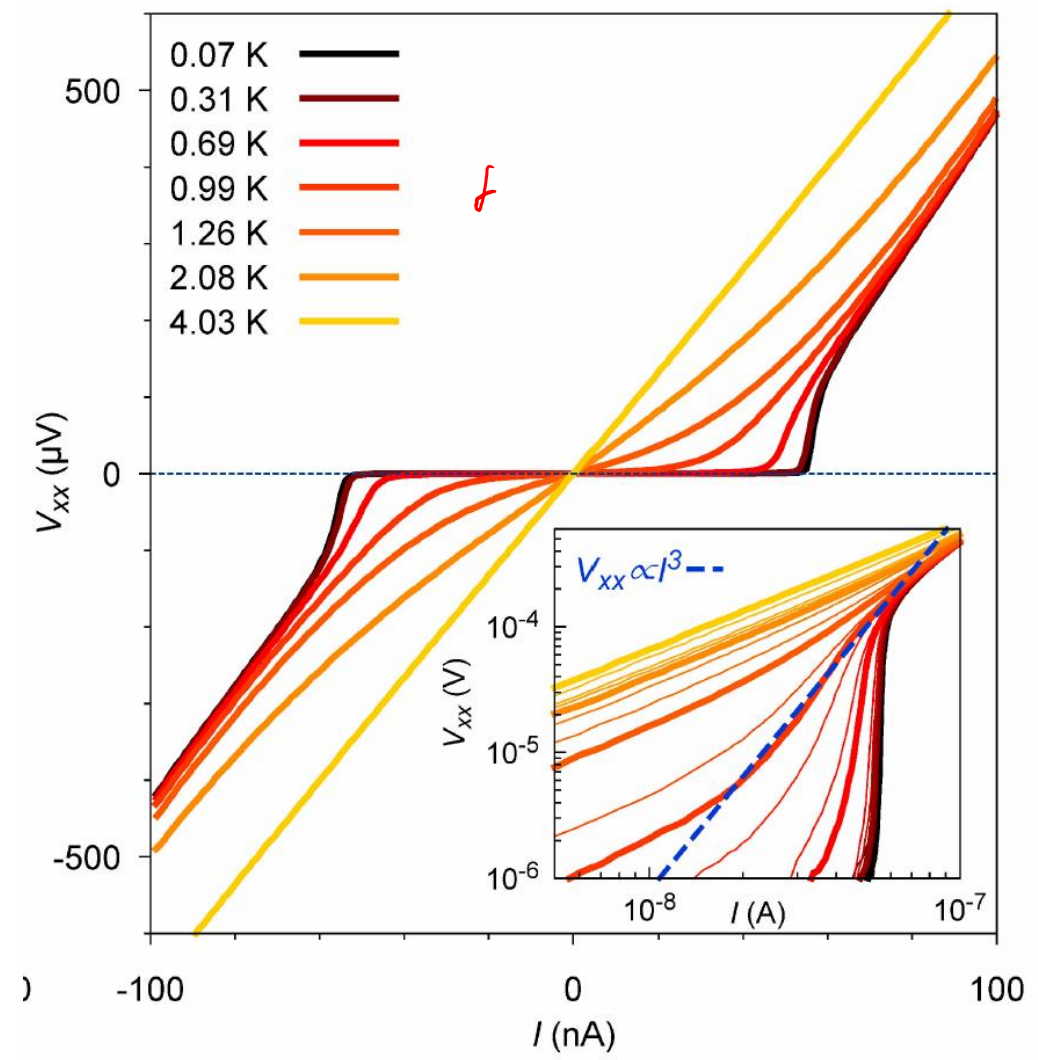
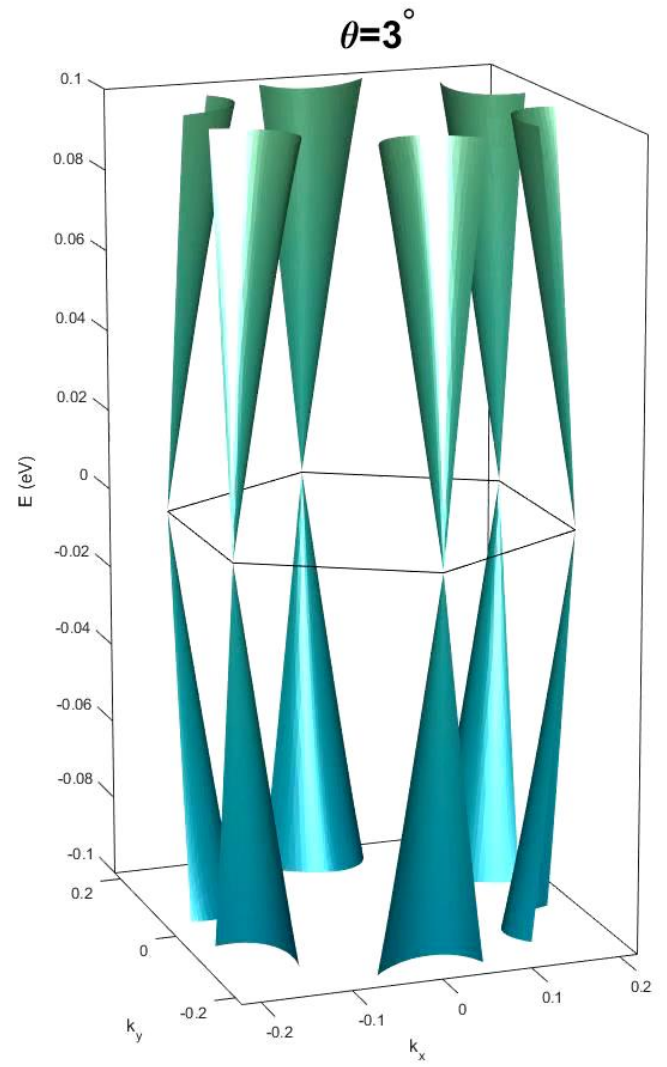
(c) Few Layer Graphene



(d) Graphite



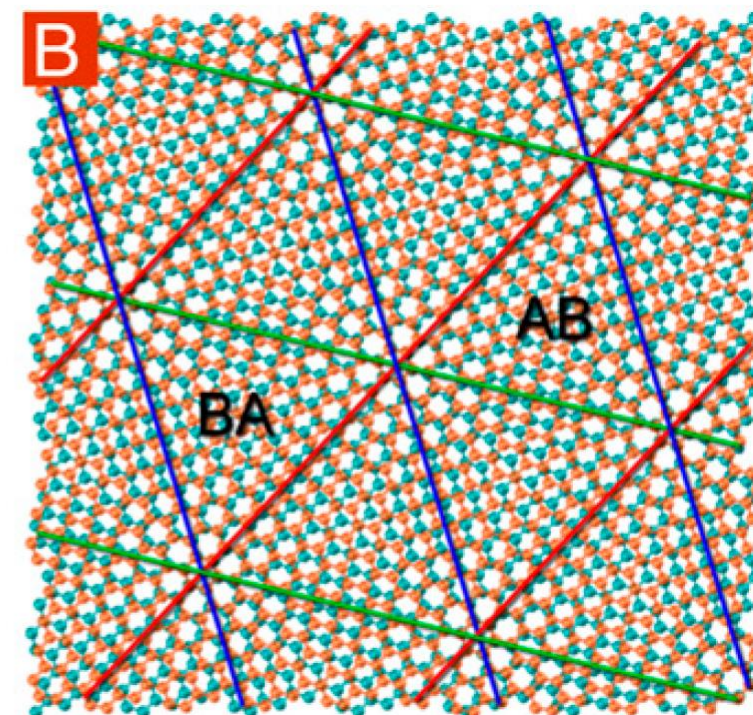
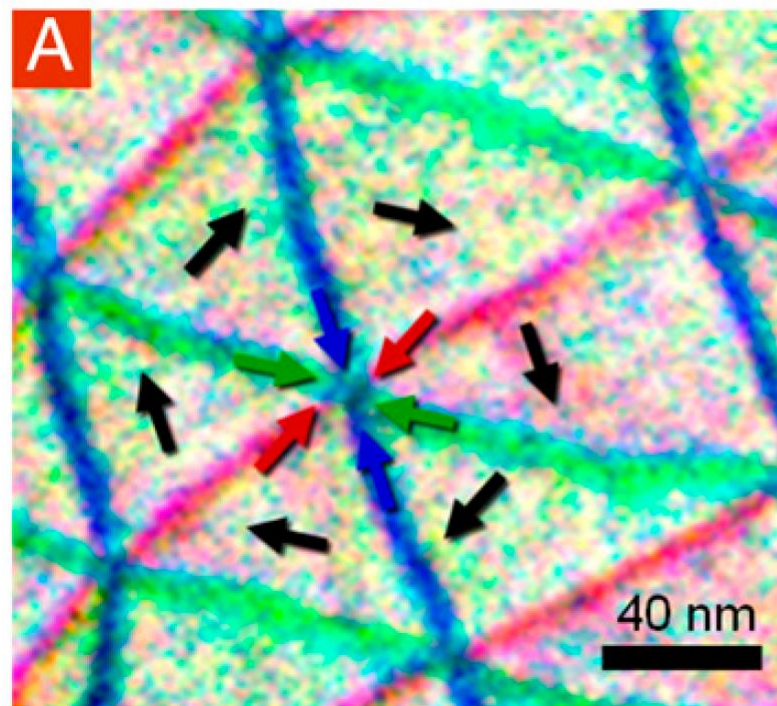
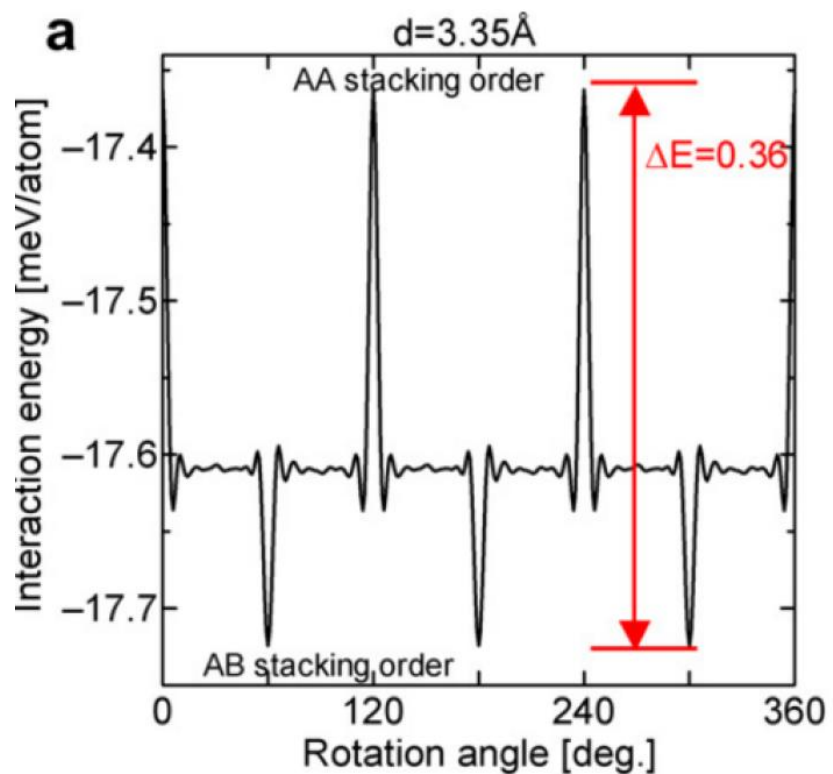


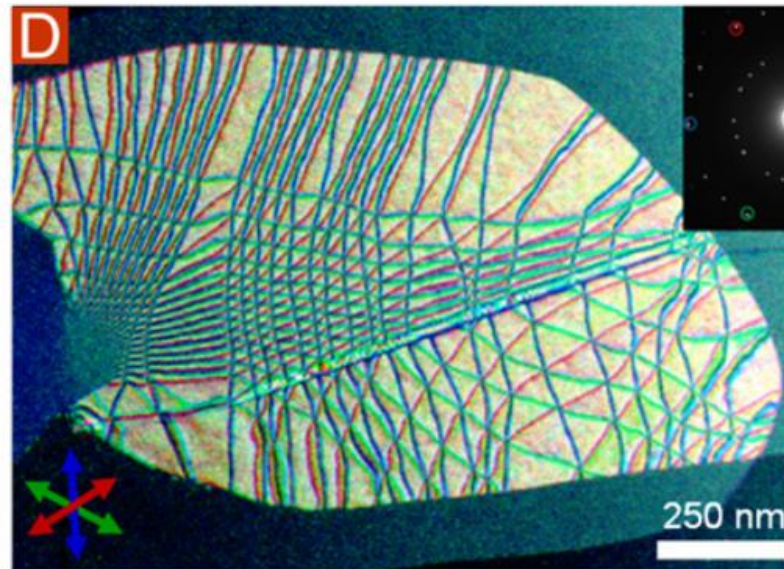
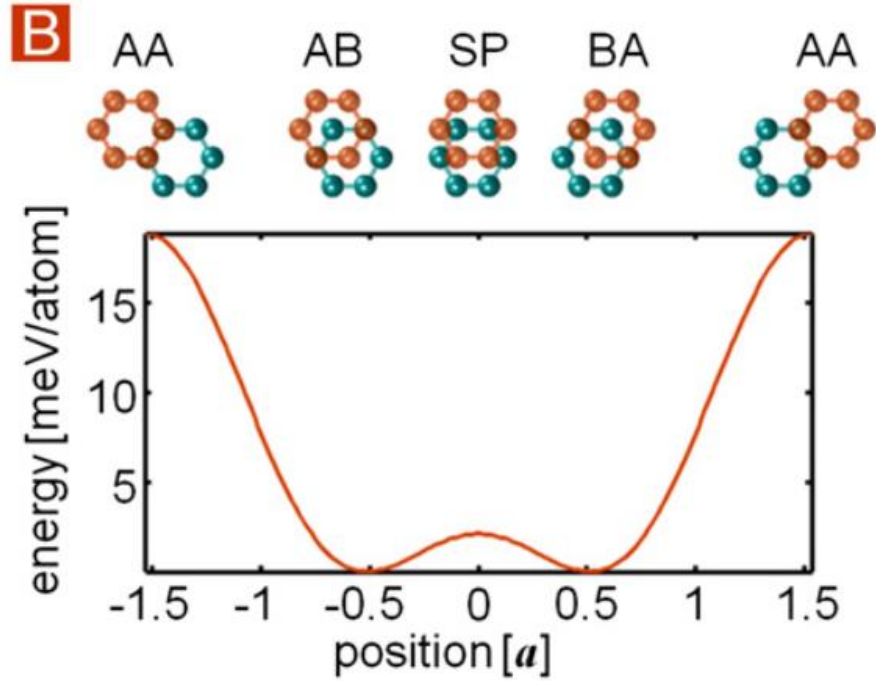
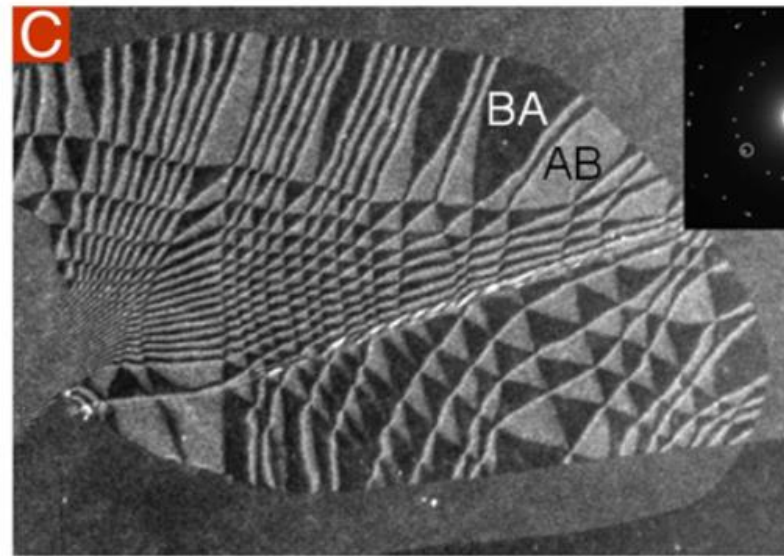
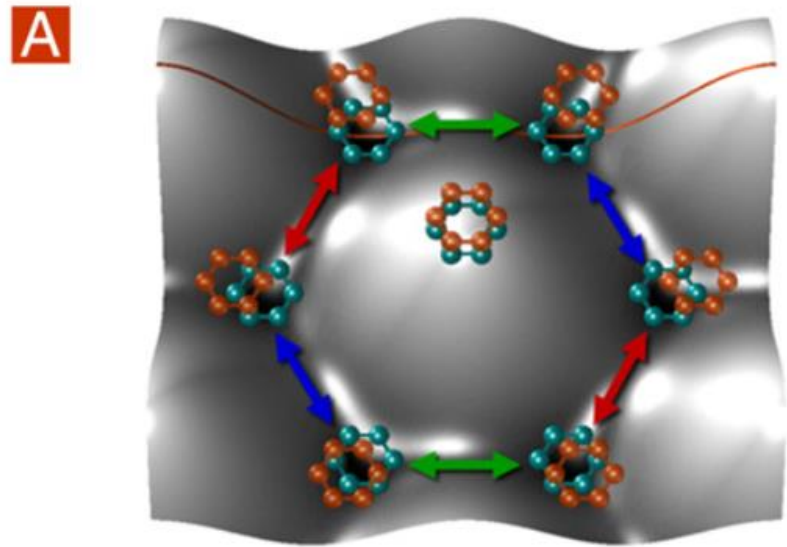


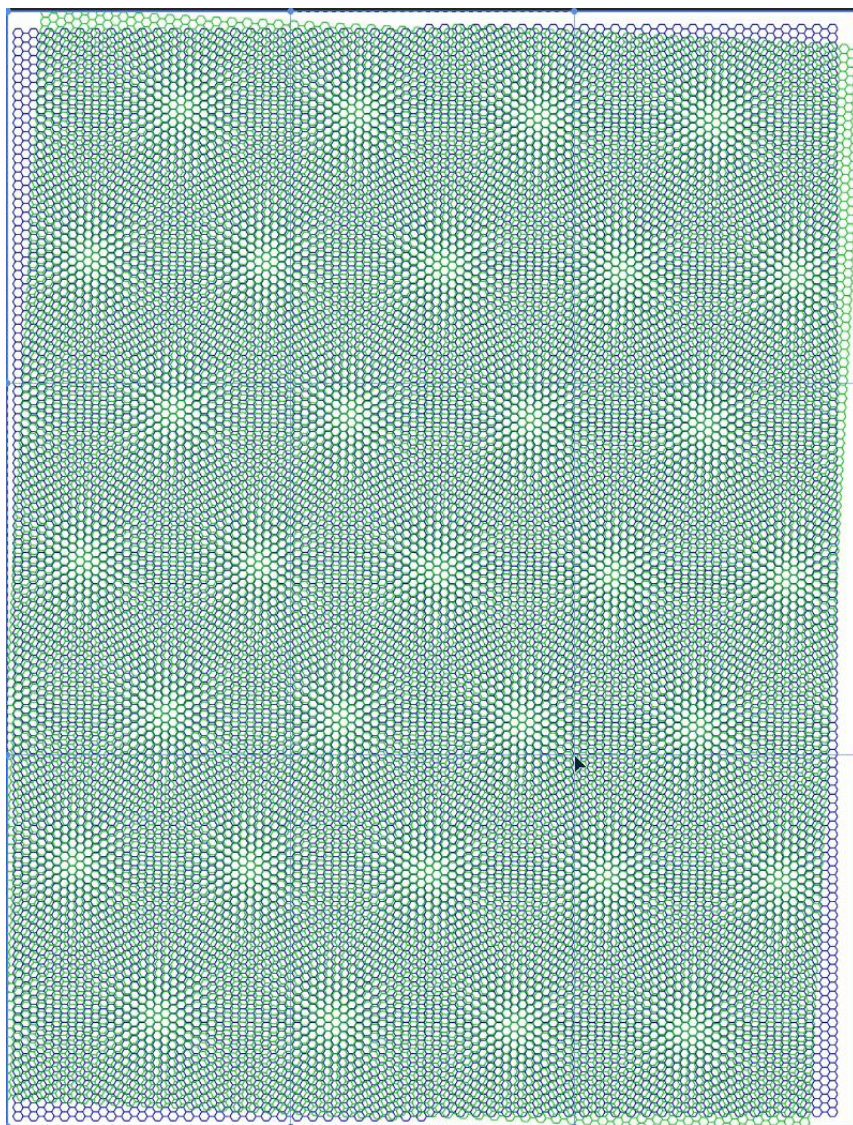
Cao, Nature 556, pages 43–50, 2018

Strain solitons and topological defects in bilayer graphene

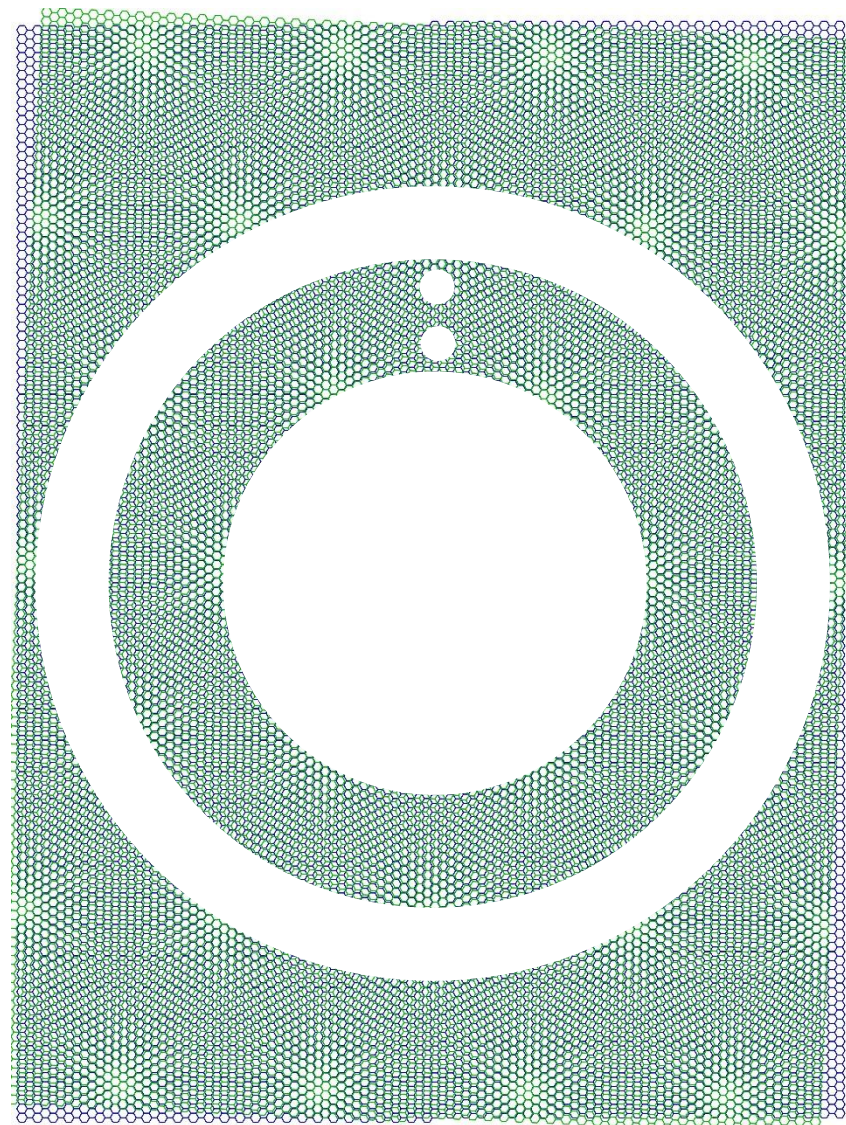
Jonathan S. Alden^a, Adam W. Tsen^a, Pinshane Y. Huang^a, Robert Hovden^a, Lola Brown^b, Jiwoong Park^{b,c}, David A. Muller^{a,c}, and Paul L. McEuen^{c,d,1}





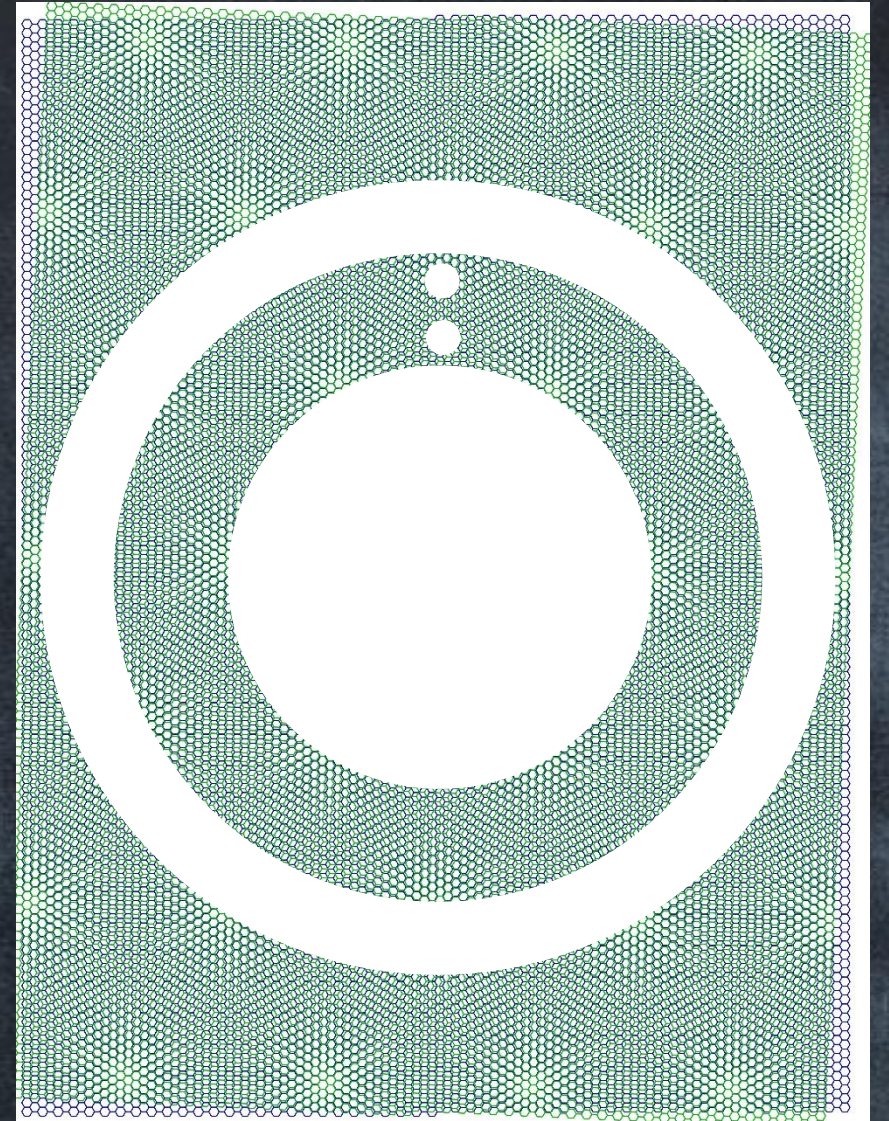


Upscaling

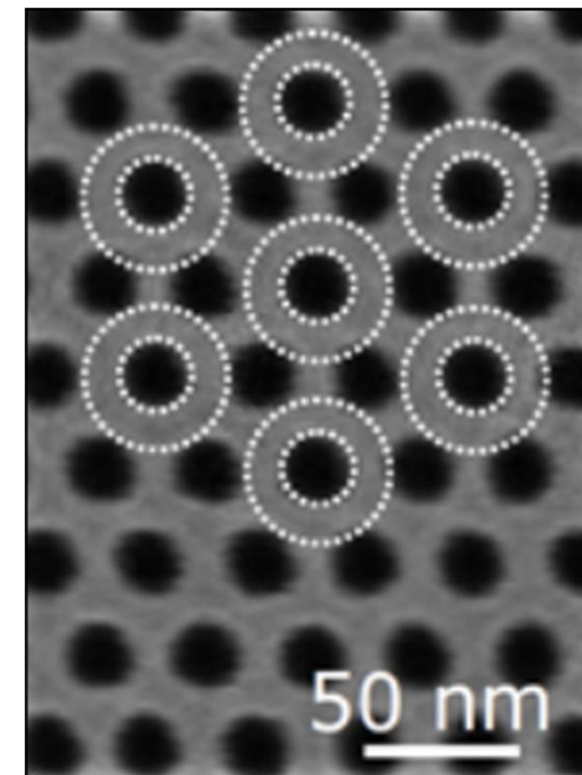
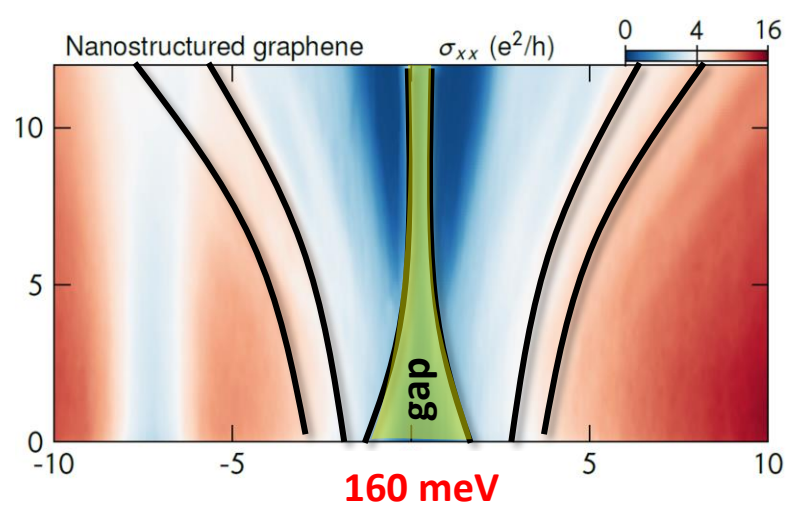
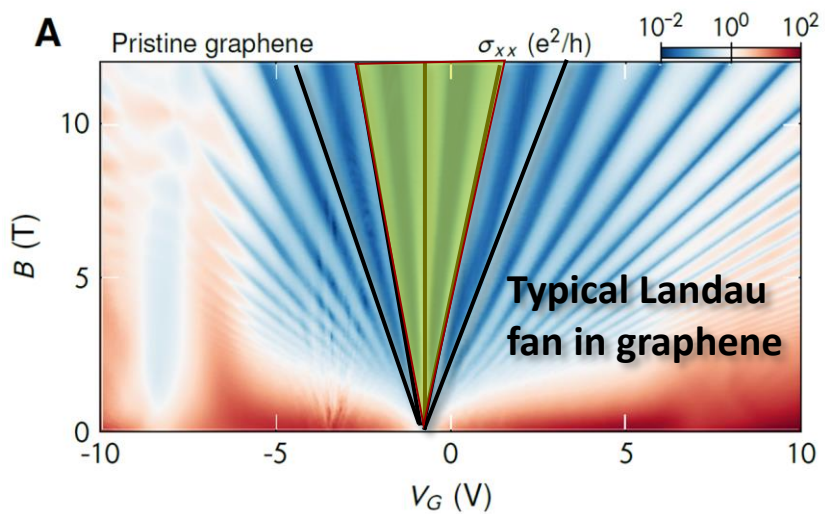
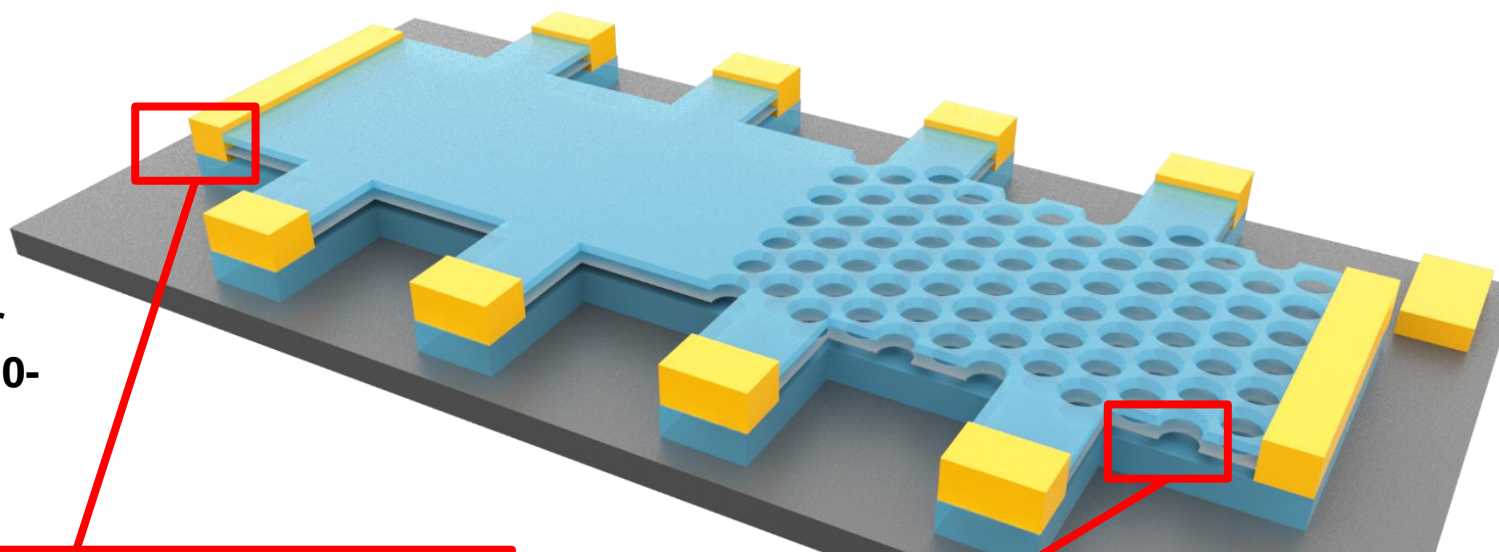


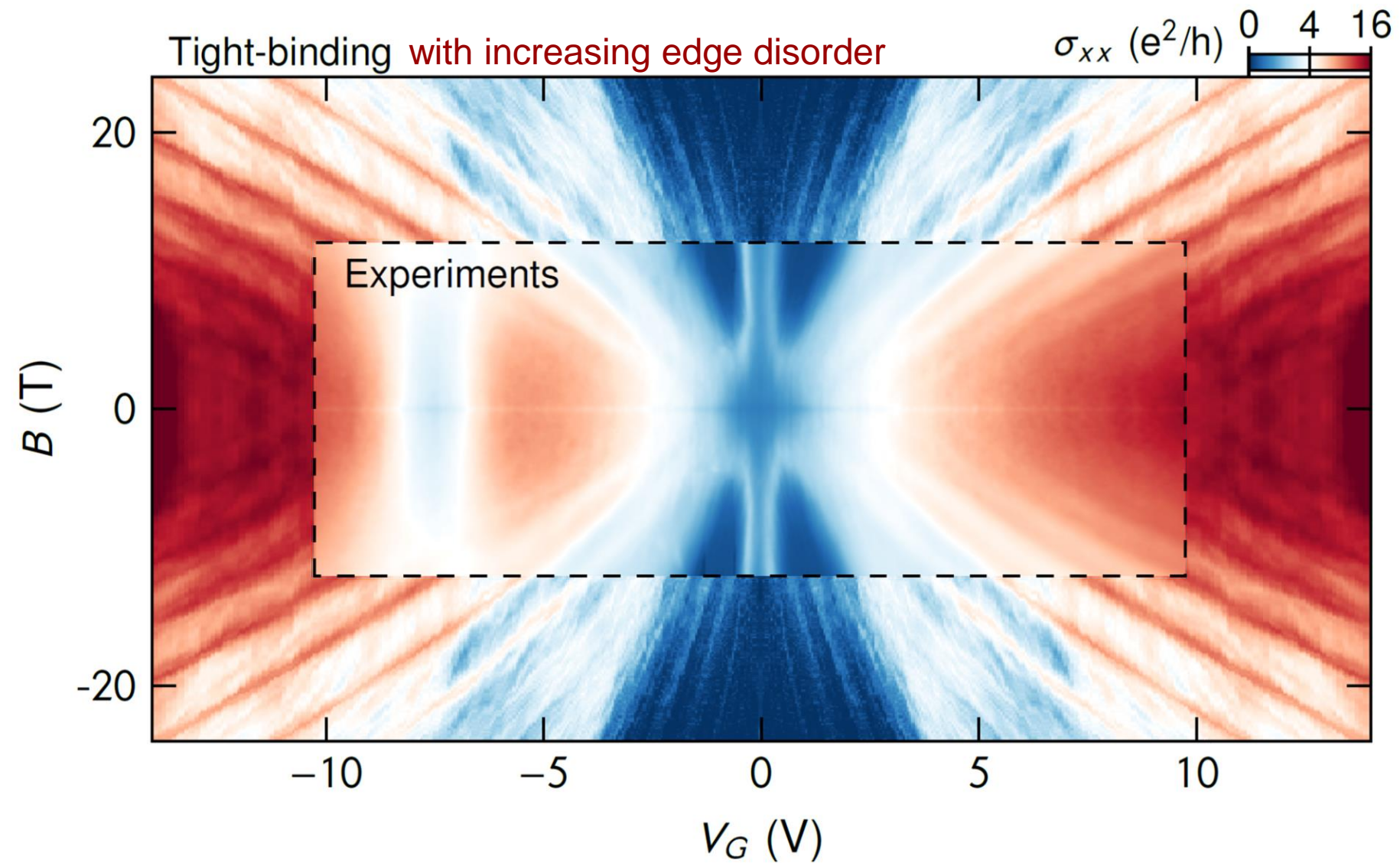
Patterning

3. vdw epitaxy -
patterning?

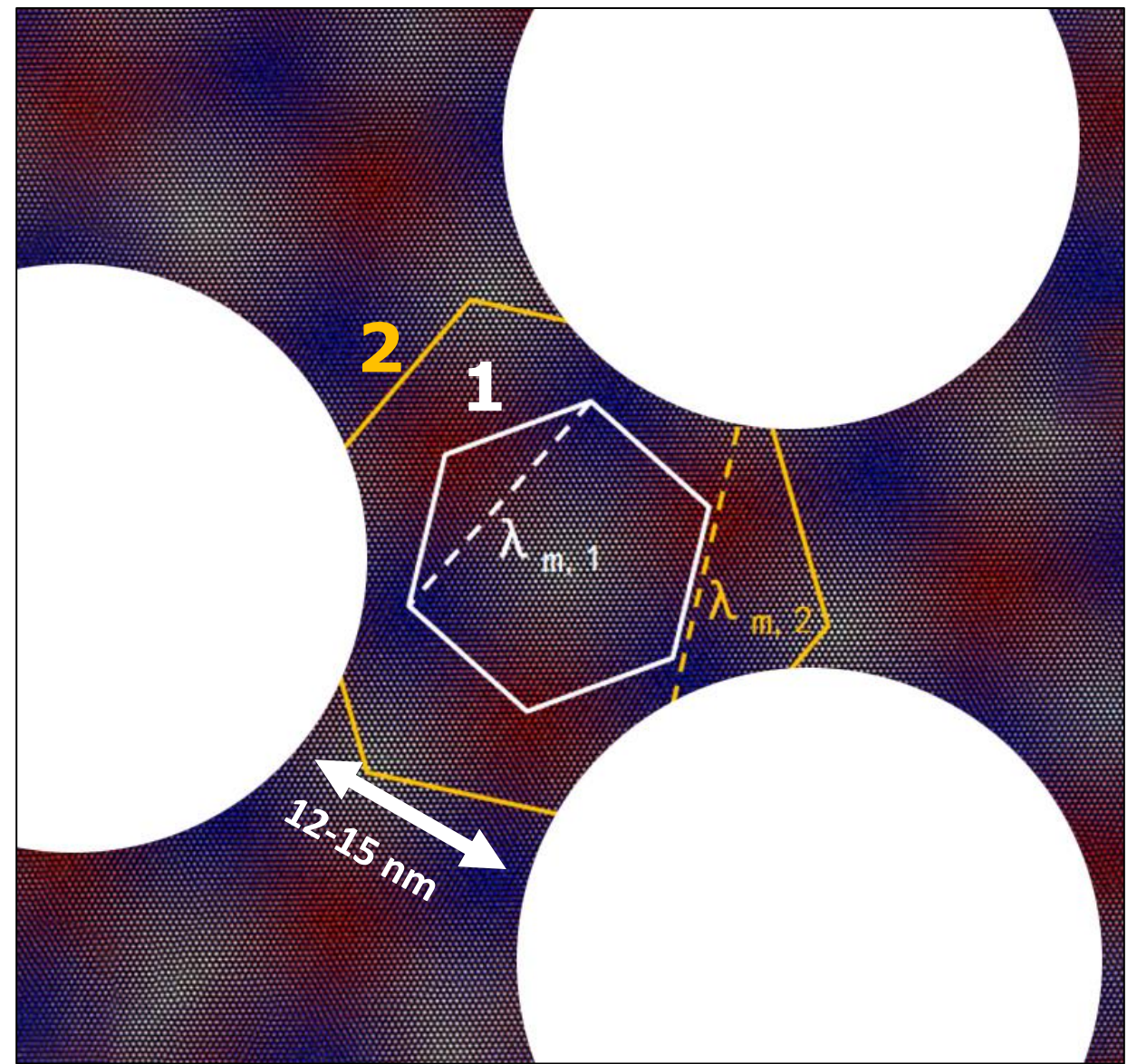
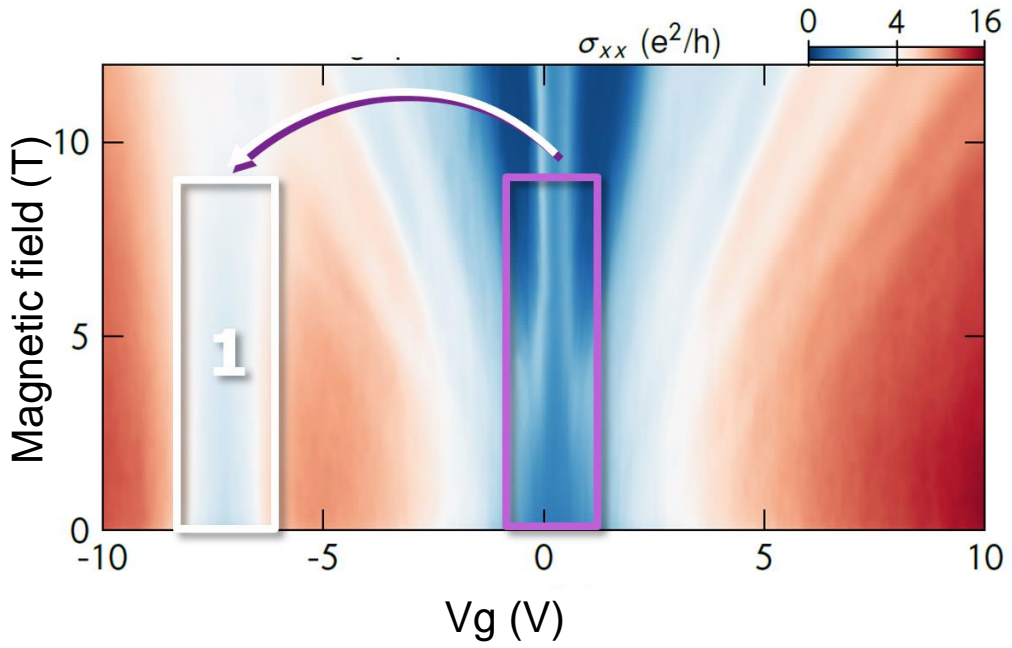
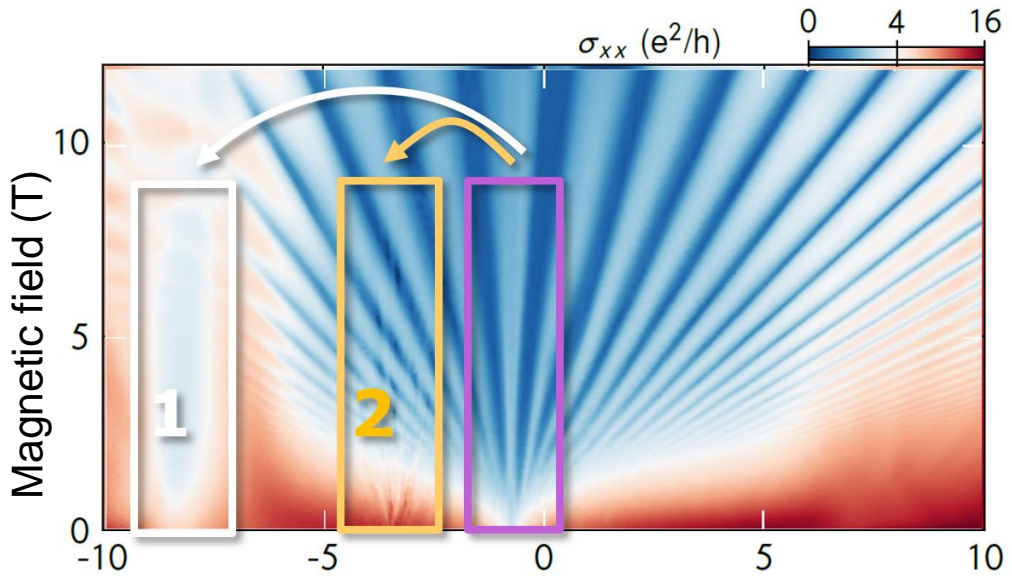


Mobility :
800 cm²/Vs
2 orders of
magnitude better
than for typical 10-
15 nm
constrictions



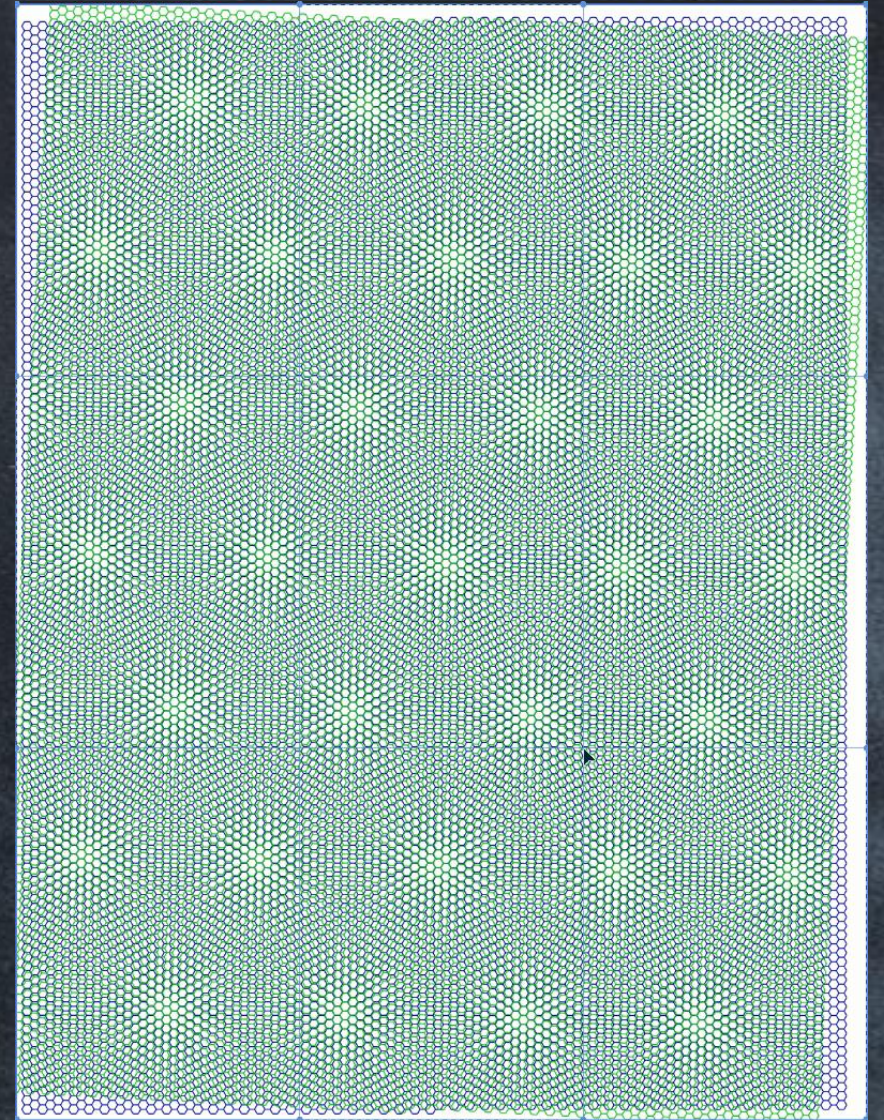


Moiré bandstructure – before and after patterning



$$\lambda_{m,1} = 10.2 \text{ nm and } \lambda_{m,2} = 17.2 \text{ nm} \approx \sqrt{3} \lambda_{m,1}$$

4. vdw epitaxy :
up-scaling?





2000 2D materials and counting

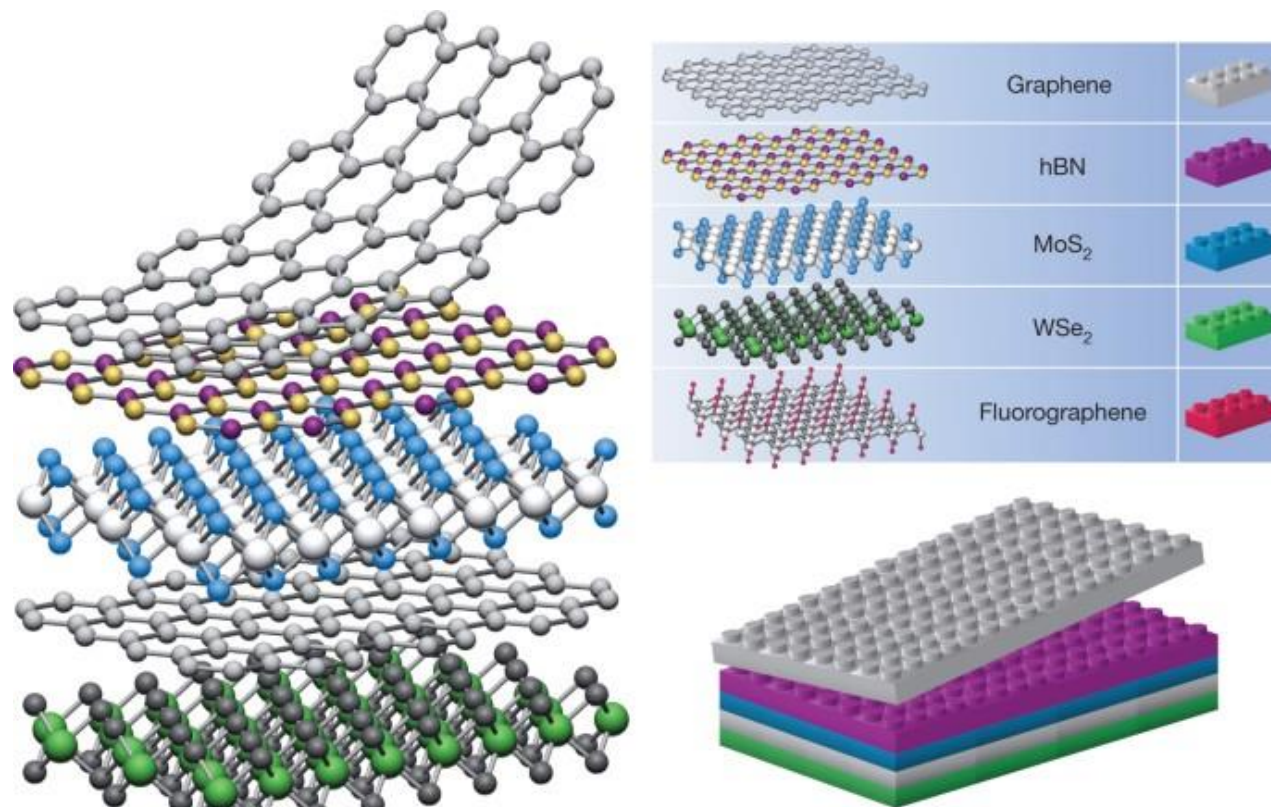
EPFL scientists identified more than 1000 2D materials. ©EPFL/C. Pizzi

[SKIP](#)

PERSPECTIVE

Van der Waals heterostructures

A. K. Geim^{1,2} & I. V. Grigorieva¹

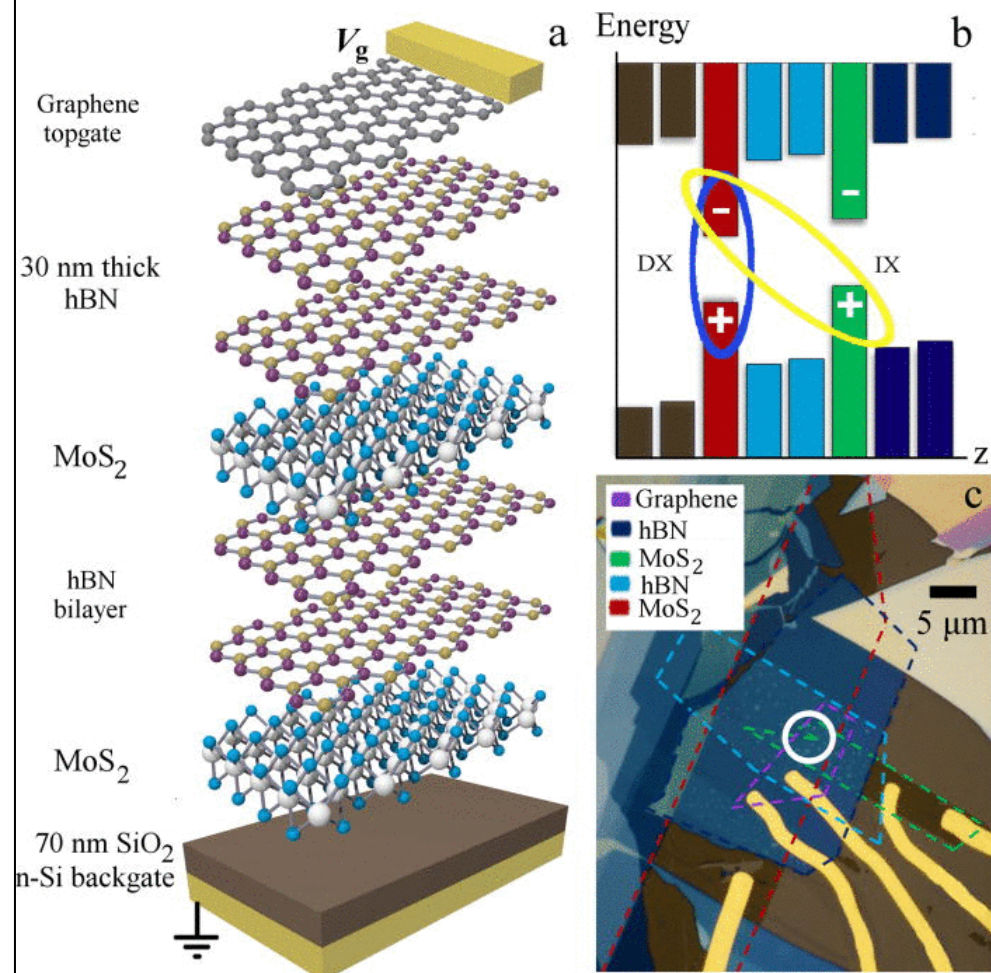


Control of excitons in multi-layer van der Waals heterostructures

E. V. Calman,^{1,a)} C. J. Dorow,¹ M. M. Fogler,¹ L. V. Butov,¹ S. Hu,² A. Mishchenko,² and A. K. Geim²

¹Department of Physics, University of California at San Diego, La Jolla, California 92093-0319, USA

²School of Physics and Astronomy, University of Manchester, Manchester M13 9PL, United Kingdom



C2DB



The Computational 2D Materials Database

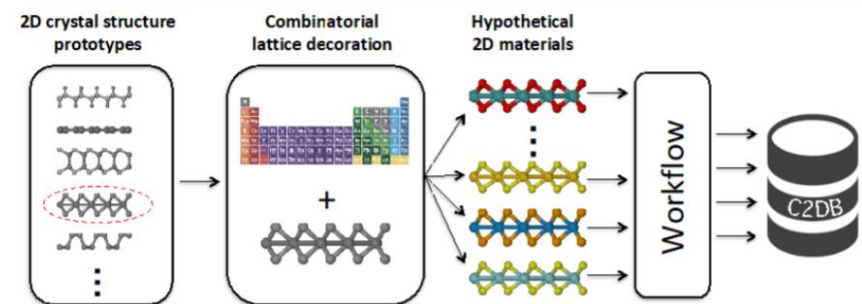


Figure 2. The materials in the C2DB are initially generated by decorating an experimentally known crystal structure prototype with atoms chosen from a (chemically reasonable) subset of the periodic table.

Search formula e.g. MoS₂



Structure prototype:

Class of material:

Dynamic stability: -

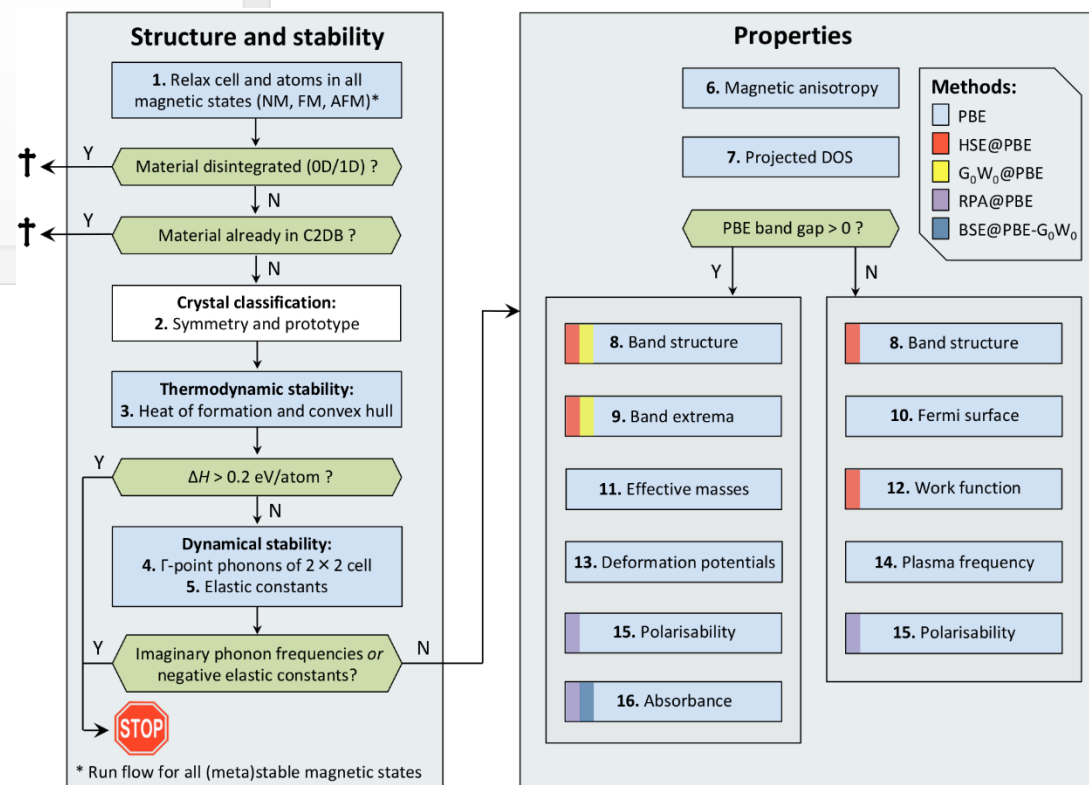
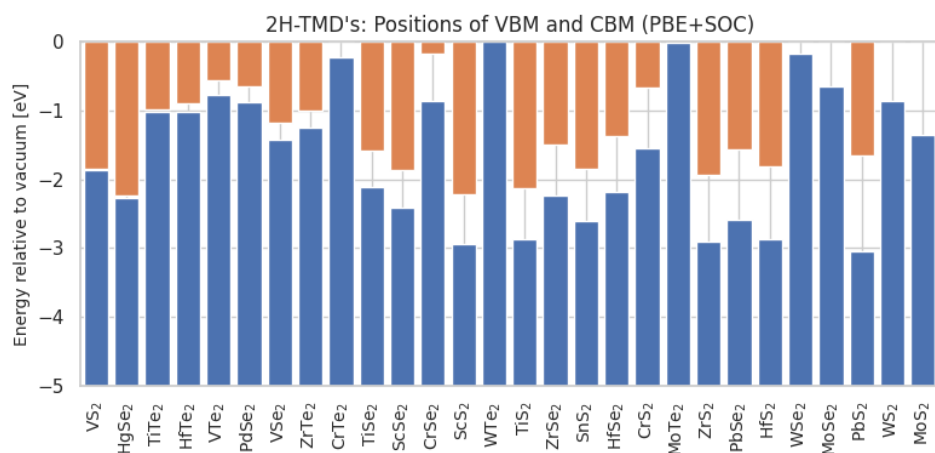
Thermodynamic stability: -

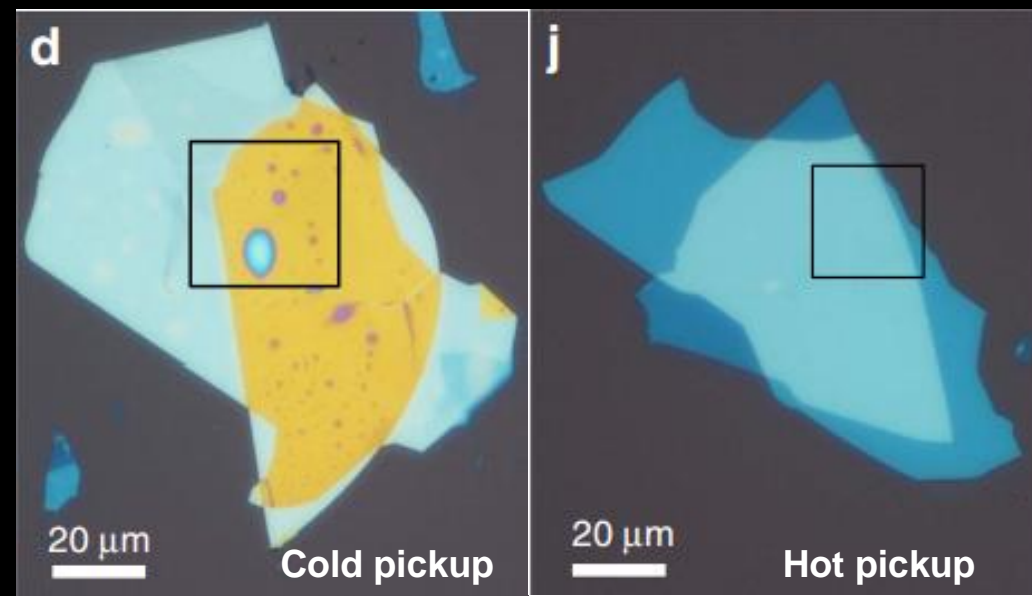
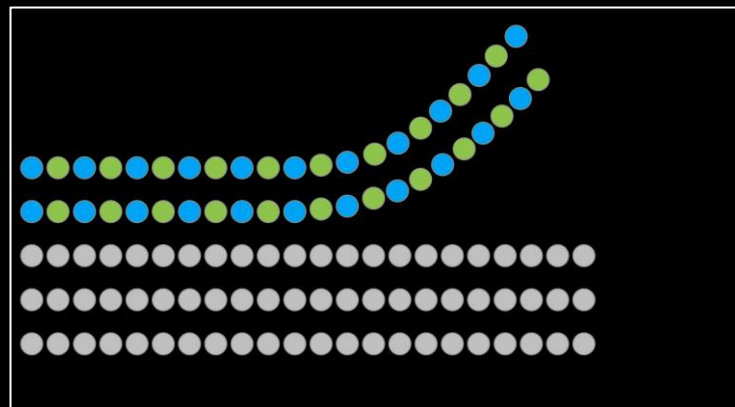
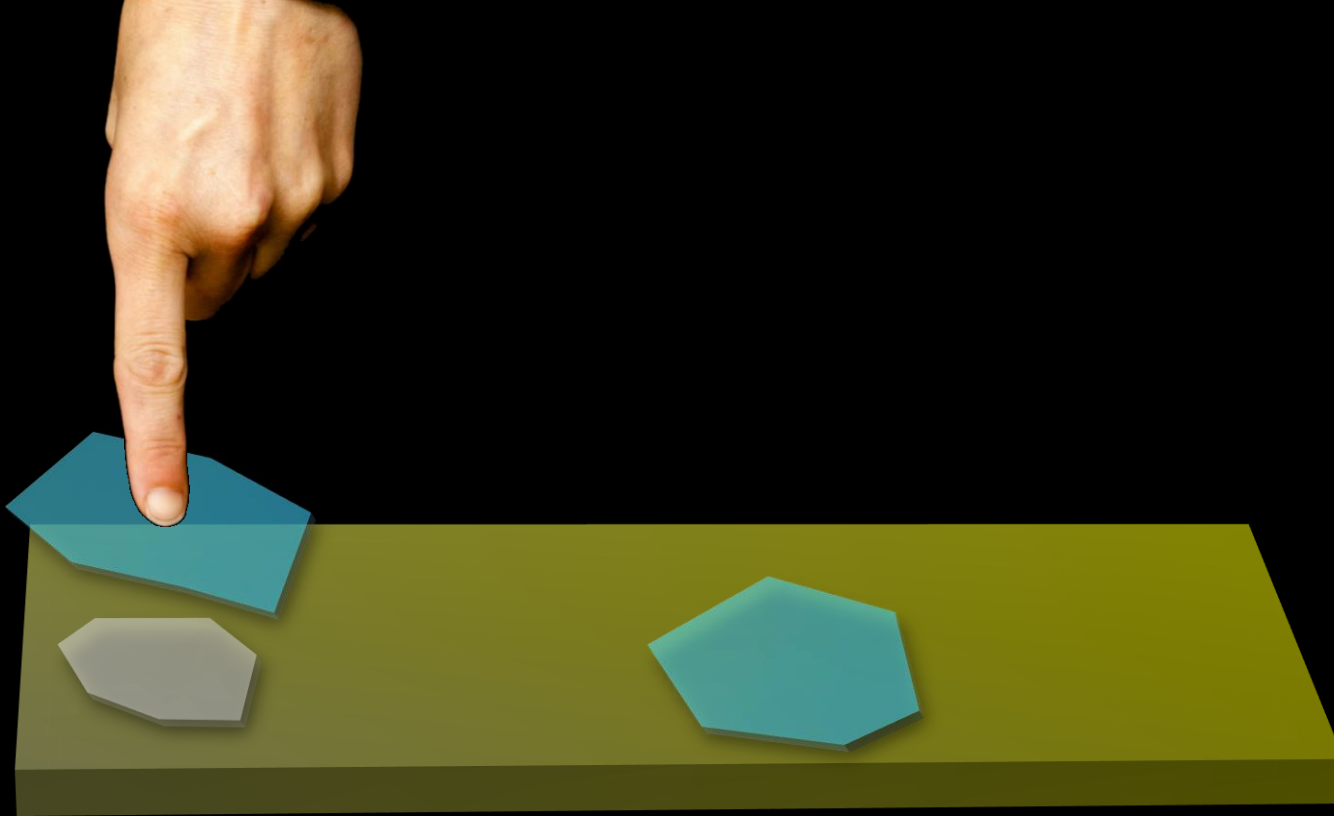
Magnetic state:

Band gap range [eV]: -

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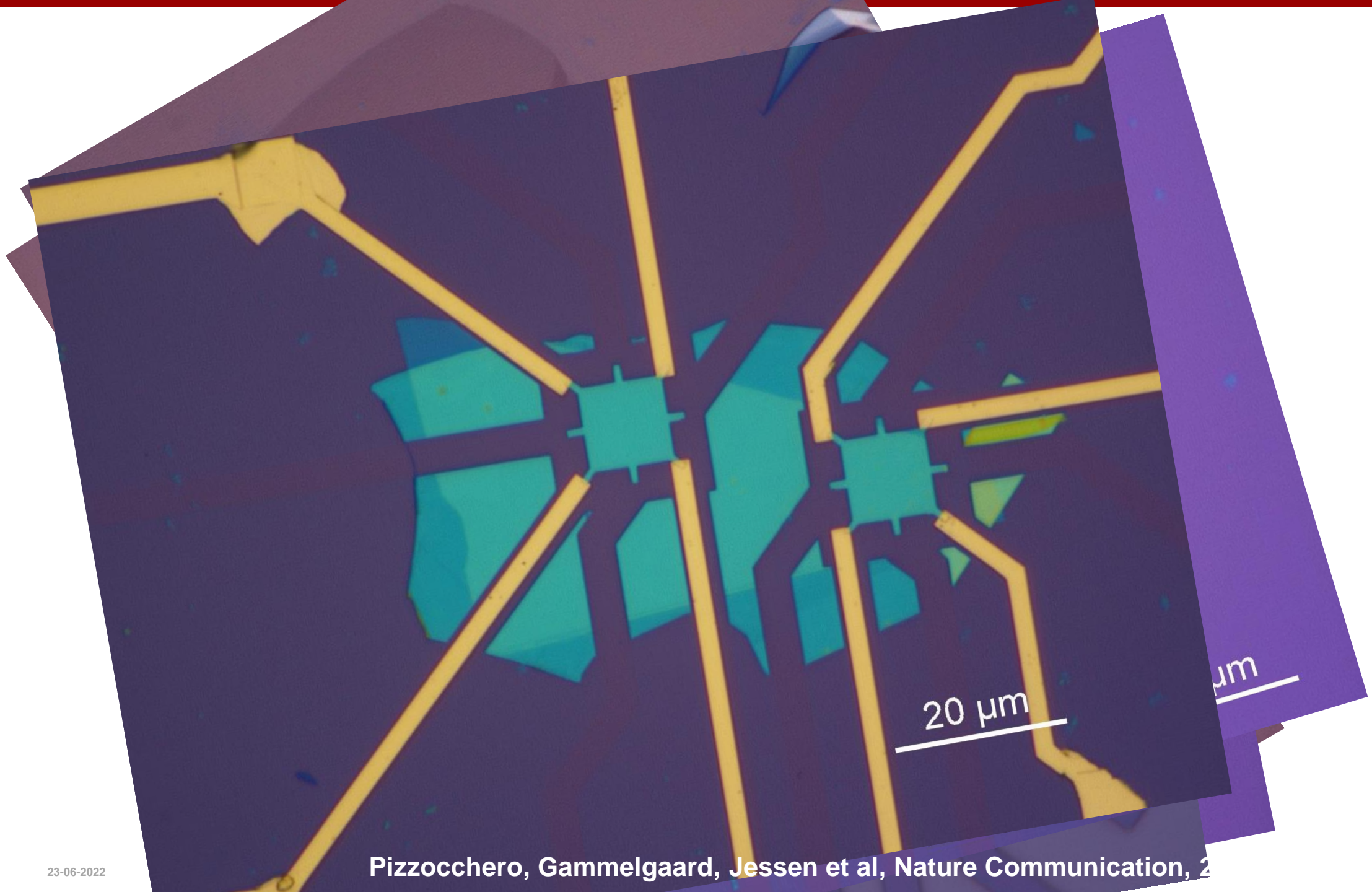
DOI: 10.1038/ncomms11894

OPEN

The hot pick-up technique for batch assembly of van der Waals heterostructures






Filippo Pizzocchero¹, Lene Gammelgaard¹, Bjarke S. Jessen¹, José M. Caridad¹, Lei Wang², James Hone³, Peter Bøggild¹ & Timothy J. Booth¹

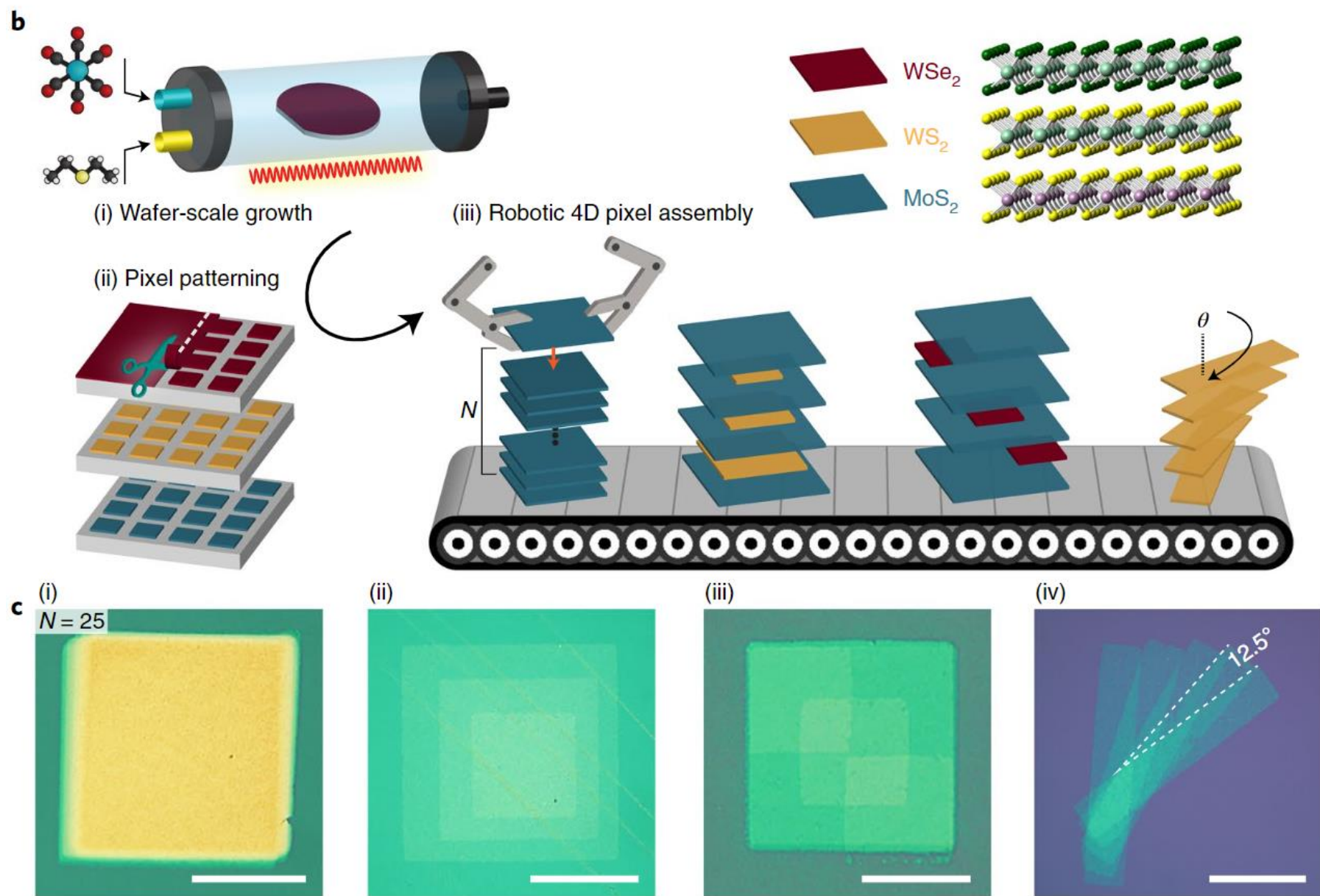
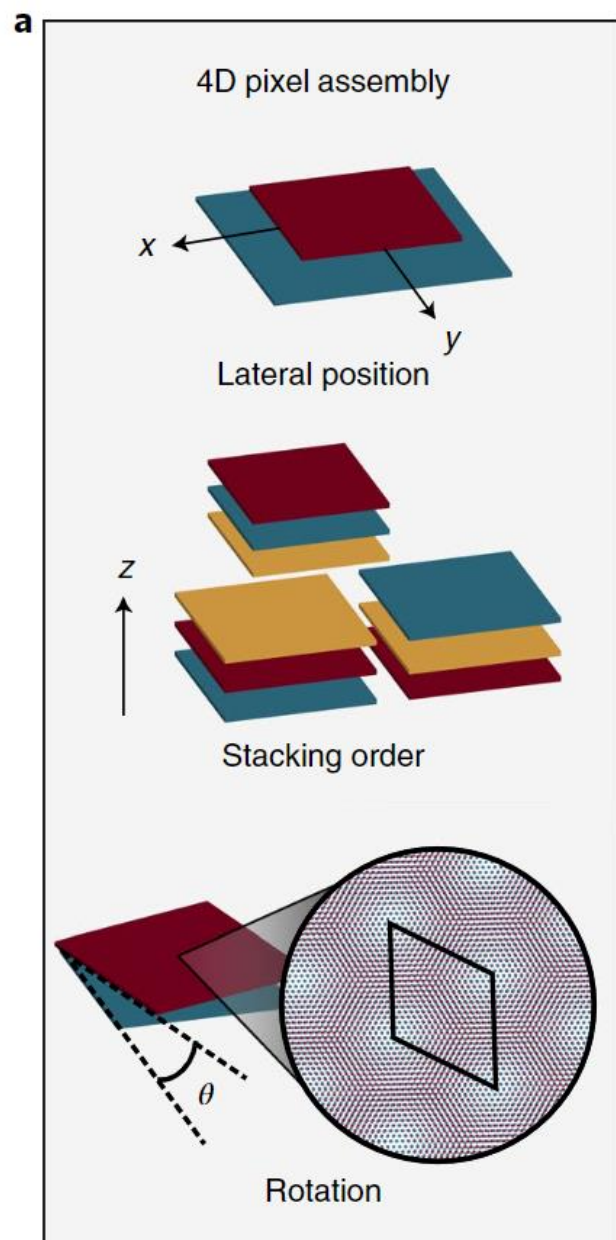
The assembly of individual two-dimensional materials into van der Waals heterostructures enables the construction of layered three-dimensional materials with desirable electronic and optical properties. A core problem in the fabrication of these structures is the formation of clean interfaces between the individual two-dimensional materials which would affect device performance. We present here a technique for the rapid batch fabrication of van der Waals heterostructures, demonstrated by the controlled production of 22 mono-, bi- and trilayer graphene stacks encapsulated in hexagonal boron nitride with close to 100% yield. For the monolayer devices, we found semiclassical mean-free paths up to 0.9 μm, with the narrowest samples showing clear indications of the transport being affected by boundary scattering. The presented method readily lends itself to fabrication of van der Waals heterostructures in both ambient and controlled atmospheres, while the ability to assemble pre-patterned layers

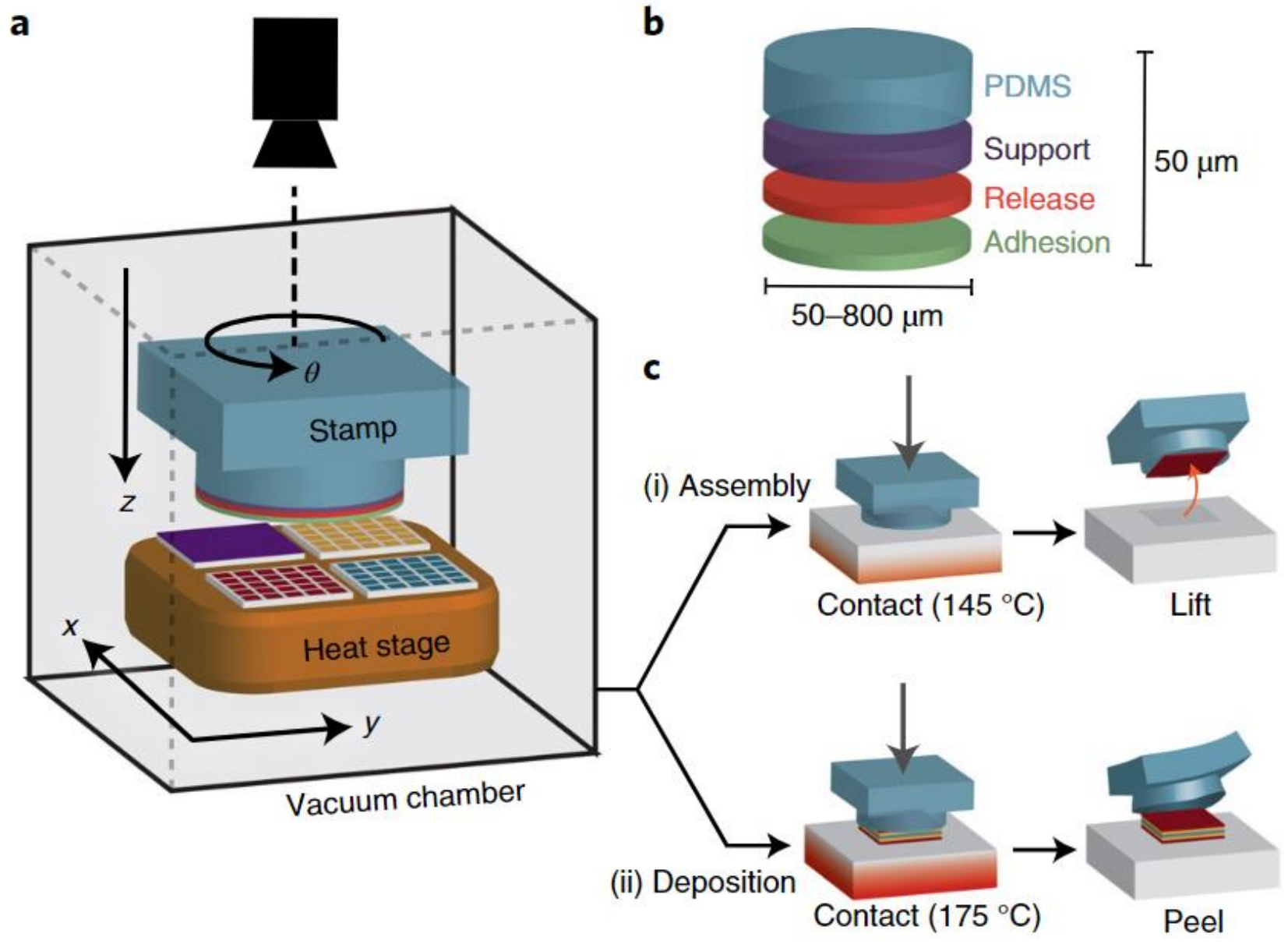


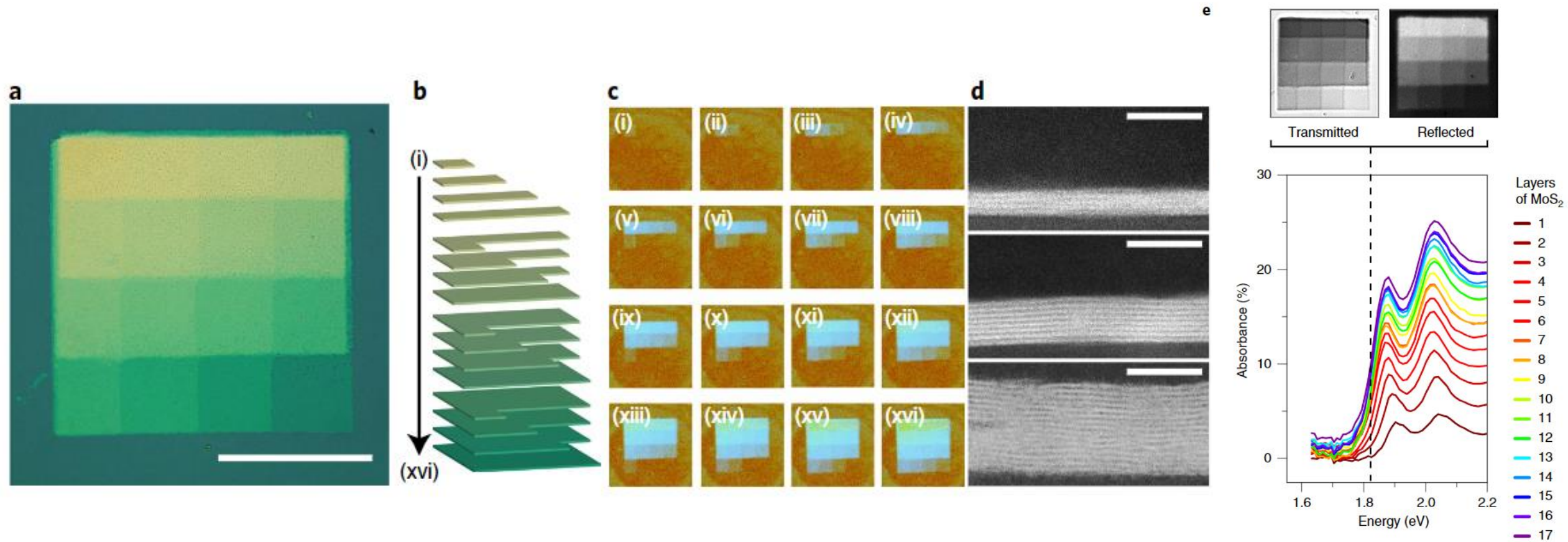


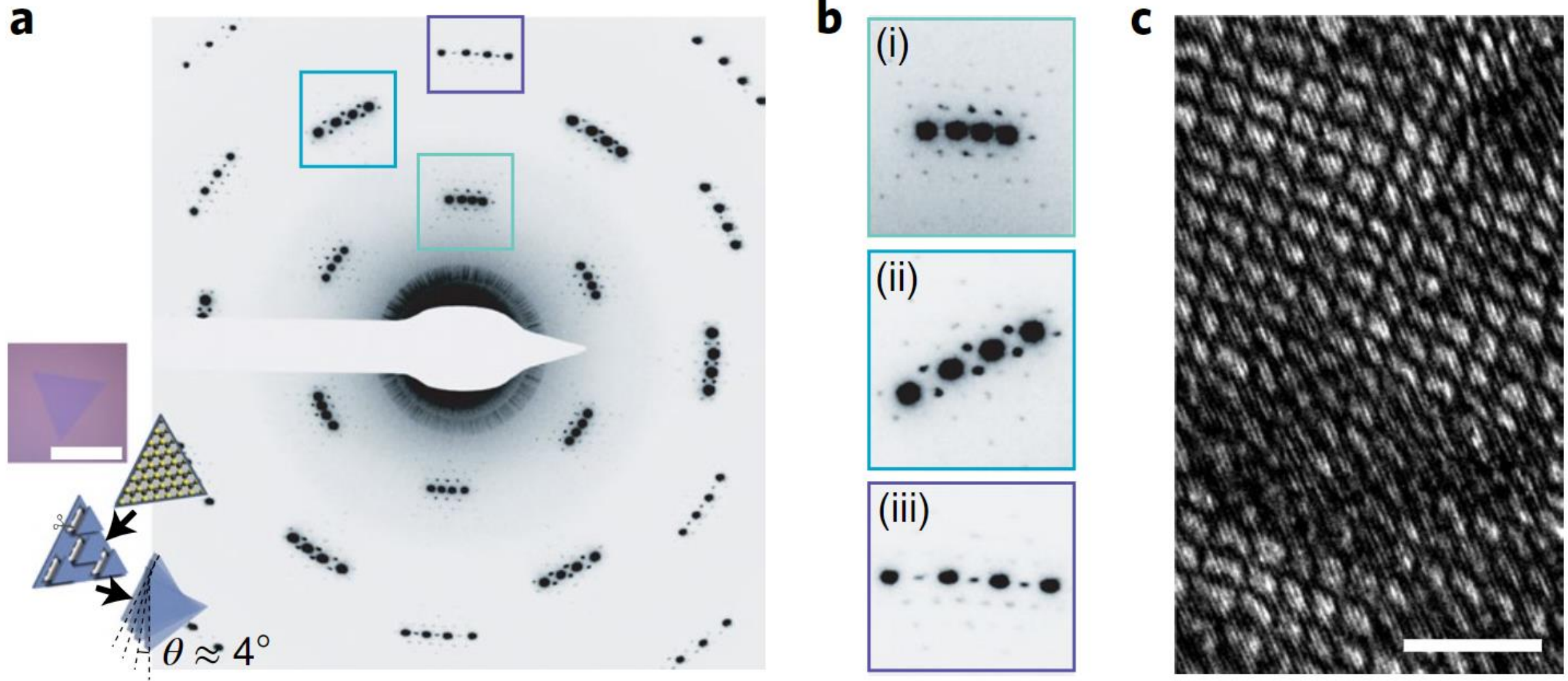
Robotic four-dimensional pixel assembly of van der Waals solids

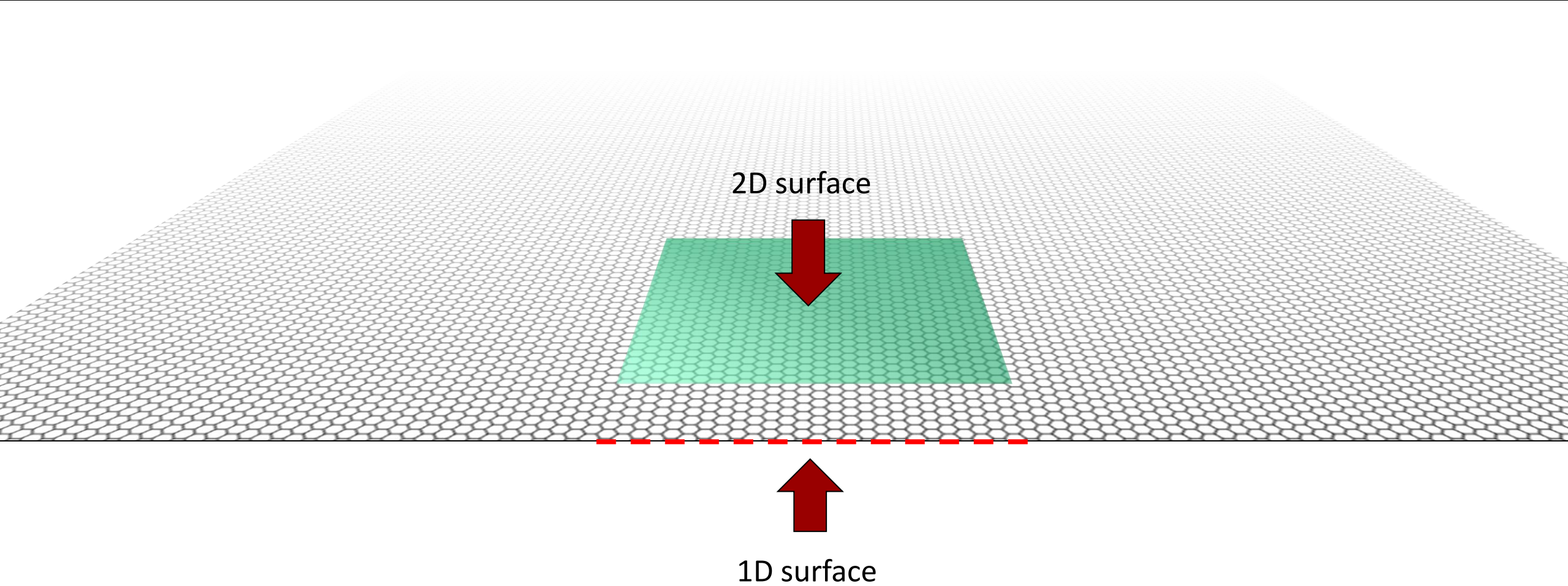
Andrew J. Mannix ^{1,9,10}, Andrew Ye^{2,10}, Suk Hyun Sung ³, Ariana Ray⁴, Fauzia Mujid⁵, Chibeom Park⁵, Myungjae Lee¹, Jong-Hoon Kang⁵, Robert Shreiner⁶, Alexander A. High^{2,7}, David A. Muller^{4,8}, Robert Hovden ³ and Jiwoong Park ^{1,2,5} 



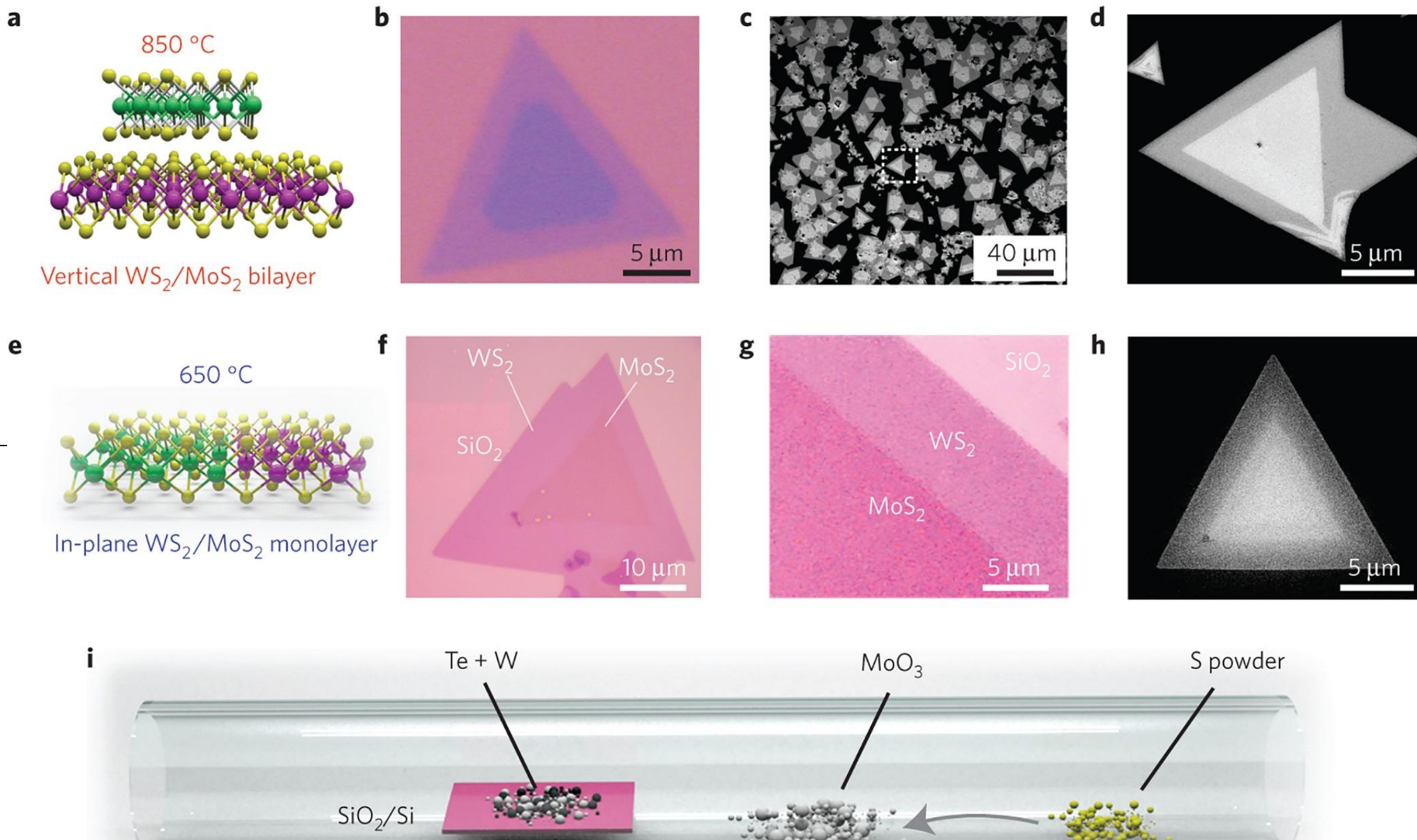








In a 2D material the bulk is a surface, and the surface is an edge



Engineering
vdw epitaxy:

materials?
Modelling?
Patterning?
Upscaling?
Applications?